



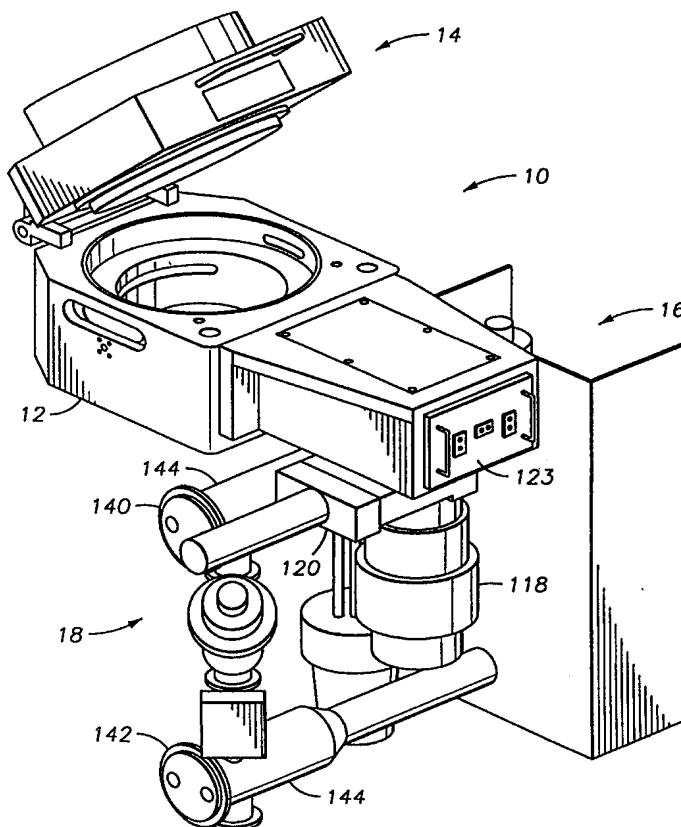
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(21) International Application Number: PCT/US98/18457 (22) International Filing Date: 3 September 1998 (03.09.98) (30) Priority Data: 08/927,700 11 September 1997 (11.09.97) US (71) Applicant: APPLIED MATERIALS, INC. [US/US]; 3050 Bowers Avenue, Santa Clara, CA 95054 (US). (72) Inventors: SOMEKH, Sasson; 25625 Moody Road, Los Altos Hills, CA 94022 (US). ZHAO, Jun; 11764 Ridge Creek Court, Cupertino, CA 95014 (US). DORNFEST, Charles; 39654 Whitecap Way, Fremont, CA 94538 (US). SAJOTO, Talex; 1373 Teakwood Drive #94, San Jose, CA 95128 (US). SELYUTIN, Leonid; 1226 Breckenridge Street, San Leandro, CA 94579 (US). KU, Vincent; 1830 Daltrey Way, San Jose, CA 95132 (US). WANG, Chris; 3557 Rue Chene D-Or, San Jose, CA 95148 (US). CHANG, Frank; 2102 Hillstone Drive, San Jose, CA 95138 (US). TANG, Po; 1239 Cardona Way, San Jose, CA 95131 (US). (74) Agents: BERNADICOU, Michael, A. et al.; Blakely, Sokoloff, Taylor & Zafman LLP, 7th floor, 12400 Wilshire Boulevard, Los Angeles, CA 90025 (US).		(81) Designated States: JP, KR, European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE). Published <i>Without international search report and to be republished upon receipt of that report.</i>

(54) Title: VAPORIZATION AND DEPOSITION APPARATUS AND PROCESS

(57) Abstract

The invention relates to an apparatus and process for the vaporization of liquid precursors and deposition of a film on a suitable substrate. Particularly contemplated is an apparatus and process for the deposition of a metal-oxide film, such as a barium, strontium, titanium oxide (BST) film, on a silicon wafer to make integrated circuit capacitors useful in high capacity dynamic memory modules.



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Claims

1. A process chamber for depositing a film, comprising:
 - a) a chamber body forming an enclosure having one or more temperature controlled surfaces;
 - b) a lid movably mounted on the chamber body, the lid having a heated main body and an outer temperature controlled collar;
 - c) a heated gas distribution assembly comprising a gas manifold connected to a gas distribution member, the gas manifold adapted to deliver one or more gases into the gas distribution member, and;
 - d) an exhaust port connected to the chamber body, the exhaust port having a temperature controlled liner disposed therein.
2. The process chamber of claim 1 wherein the chamber body defines one or more gas passages therethrough.
3. The process chamber of claim 2 wherein the one or more gas passages comprise a channel formed in the chamber body and at least one of the passages comprise a temperature controlled feedthrough positionable within the channel, the temperature controlled feedthrough having a heating element disposed therein.
4. The process chamber of claim 3 wherein the main body of the lid is comprised of a thermally conductive material and a thermocouple is disposed in the main body of the lid to monitor the temperature of the lid and adjacent gas distribution assembly.
5. The chamber of claim 3 wherein the one or more gas passages comprise an inlet and an outlet and the outlet is adapted to form a sealed gas passage with a gas passage in the gas manifold.
6. The chamber of claim 4 wherein the main body of the lid is maintainable at a temperature greater than about 20° C and the outer collar is maintainable at a

temperature less than about 250° C.

7. The chamber of claim 6 further comprising a coolant channel formed in the outer collar.

8. The chamber of claim 7 further comprising a thermally isolatable seal disposed between the outer collar of the lid and the chamber body.

9. The chamber of claim 1 wherein the one or more temperature controlled surfaces comprise a liner positionable within the chamber.

10. The chamber of claim 9 wherein the liner is supported on one or more supports disposed on the lower portion of the liner.

11. The chamber of claim 10 wherein the liner is thermally floating in the chamber.

12. The chamber of claim 9 wherein the liner comprises a heating element disposed therein and the liner is supported in the chamber on one or more supports and the heating element is connected to a power source.

13. The chamber of claim 12 wherein the liner is comprised of a material selected from the group consisting of titanium, stainless steel, nickel, aluminum, aluminum oxide, barium strontium titanate, aluminum nitride, silicon carbide or combinations thereof.

14. The chamber of claim 13 wherein the liner is maintainable at a temperature of at least about 50° C.

15. The chamber of claim 1 wherein the lid defines a channel between the main body of the lid and the outer temperature controlled collar to define a thermally restrictive conducting outer temperature controlled collar.

16. The chamber of claim 15 further comprising a support member disposed in the channel.
17. The chamber of claim 16 wherein the lid is comprised of aluminum and the support member is comprised of stainless steel.
18. The chamber of claim 17 wherein the lid further comprises a lower mounting surface on the outer collar having one or more cooling passages formed therein.
19. The chamber of claim 18 wherein the lid further comprises a heating element disposed adjacent the main body member.
20. The chamber of claim 19 wherein the lid further comprises a cooling plate disposed on the main body member.
21. The chamber of claim 1 wherein the chamber body further comprises one or more gas channels formed therethrough and connected to the one or more gas manifolds.
22. The chamber of claim 21 further comprising a vaporizer connected to at least one of the gas channels formed in the chamber body.
23. The chamber of claim 22 wherein the vaporizer comprises:
- a) one or more inlets;
 - b) a temperature controlled body member defining a plurality of fluid passages having a plurality of vaporizing surfaces disposed therein; and
 - c) one or more outlets connected to the one or more fluid passages.
24. The chamber of claim 23 wherein the body member of the vaporizer includes one or more heating elements connected thereto.
25. The chamber of claim 24 wherein the vaporizer further comprises one or more

thermocouples disposed therein to monitor the temperature of the vaporizer.

26. The chamber of claim 23 wherein the inlet comprises a nozzle and a circumferential fluid passage disposed around the nozzle and the plurality of vaporizing surfaces comprise a plurality of fins disposed along one or more fluid passages.

27. The chamber of claim 22 further comprising one or more pressurized ampules connected to the vaporizer.

28. The chamber of claim 27 wherein the one or more ampules have a tapered inner chamber lower portion.

29. The chamber of claim 28 wherein the ampule further comprises a volume detector.

30. The chamber of claim 29 wherein the volume detector comprises an ultra-sonic type detector.

31. The chamber of claim 27 wherein the ampule is chargeable up to about 500psig.

32. The chamber of claim 23 further comprising a bypass line connected between the one or more outlets of the vaporizer and the one or more fluid channels formed in the chamber body.

33. The chamber of claim 32 wherein the bypass line is connected to an exhaust pump and a cold trap is disposed in the bypass line upstream from the exhaust pump.

34. The chamber of claim 33 further comprising a valve member disposed between the outlet, the fluid channels and the bypass line.

35. The chamber of claim 1 further comprising a substrate support member

disposed in the chamber.

36. The chamber of claim 35 wherein the substrate support member comprises an electrode disposed therein and a power source connected to the electrode.

37. The chamber of claim 36 further comprising a shield ring disposed in the chamber around the edge of the substrate support member.

38. The chamber of claim 37 wherein the shield ring is comprised of a material having a coefficient of expansion approximately equal to that of the deposition material.

39. The chamber of claim 38 wherein the shield ring is comprised of a material selected from the group comprising titanium, aluminum oxide, or combinations thereof.

40. The chamber of claim 5 wherein the seal formed between the heated gas passages and the gas manifolds comprise a spring loaded seal.

41. The chamber of claim 40 wherein the spring loaded seal is comprised of Teflon.

42. The chamber of claim 1 further comprising first and second exhaust passages disposed in the exhaust port.

43. The chamber of claim 42 further comprising a high vacuum pump connected to the first exhaust passage and selectively isolatable therefrom by a valve member.

44. The chamber of claim 43 further comprising an exhaust pump connected to the second exhaust passage.

45. The chamber of claim 44 further comprising a removable cold trap disposed between the exhaust pump and the exhaust port.

46. The chamber of claim 43 wherein the valve member comprises a gate valve.
47. The chamber of claim 3 wherein the gas distribution assembly is mounted on the lid and forms a seal with the heated gas passages to provide sealed fluid flow therebetween.
48. A lid for a processing chamber, comprising:
- a) a main body defining a circumferential heat limiting channel, the main body having a chamber mounting surface disposed on an outer wall disposed outwardly from the heat limiting channel;
 - b) a heat limiting support member disposed in the channel; and
 - c) a gas distribution assembly disposed on the main body.
49. The lid of claim 48 wherein the gas distribution assembly comprises:
- a) a gas manifold disposed on the main body, the gas manifold defining one or more gas passages therein; and
 - b) a gas distribution plate connected to the gas manifold, the gas distribution plate having a first and a second gas distributing surface.
50. The lid of claim 49 wherein the gas manifold comprises a first and a second gas passage and the first and the second gas passages are connected by a restrictive passage disposed therebetween proximal one end thereof.
51. The lid of claim 50 wherein the gas distribution plate further comprises one or more heat transfer channels formed therein.
52. The lid of claim 51 wherein the lid further comprises a heating element disposed on the main body.
53. The lid of claim 52 wherein the lid further comprises a cover plate disposed on the main body.

54. The lid of claim 53 wherein the cover plate further comprises one or more heat transfer channels disposed therein.

55. The lid of claim 49 further comprising a vaporizer disposed on the main body and connected to the gas distribution assembly.

56. The lid of claim 55 wherein the gas distribution assembly comprises a gas distribution plate having an inlet and a first and a second gas distributing surface.

57. The lid of claim 56 wherein the gas distribution plate further comprises one or more heat transfer channels formed therein.

58. The lid of claim 57 wherein the lid further comprises a heating element disposed on the main body.

59. The lid of claim 58 wherein the lid further comprises a cover plate disposed on the main body.

60. The lid of claim 59 wherein the cover plate further comprises one or more heat transfer channels disposed therein.

61. The lid of claim 55 further comprising a thermocouple disposed therein and positioned adjacent to the gas manifold.

62. The lid of claim 60 further comprising a thermocouple disposed therein and positioned adjacent to the gas manifold.

63. The lid of claim 55 further comprising a heat transfer channel disposed adjacent the chamber mounting surface.

64. The lid of claim 61 further comprising a heat transfer channel disposed adjacent the chamber mounting surface.

65. The lid of claim 50 wherein the gas manifold further comprises a conductance guide disposed on the lower portion of the gas manifold which mounts the gas distribution plate.

66. The lid of claim 65 wherein the conductance guide forms a seal with the gas distribution plate to prevent gases from flowing therebetween.

67. The lid of claim 51 wherein the gas manifold comprises a first and a second gas passage and the first and the second gas passages are connected by a restrictive passage disposed therebetween proximal one end thereof.

68. The lid of claim 67 wherein the gas distribution plate further comprises one or more heat transfer channels formed therein.

69. The lid of claim 68 wherein the lid further comprises a heating element disposed on the main body.

70. The lid of claim 69 wherein the lid further comprises a cover plate disposed on the main body.

71. The lid of claim 70 wherein the cover plate further comprises one or more heat transfer channels disposed therein.

72. An apparatus for vaporizing one or more liquids, comprising:

- a) a body defining one or more fluid passages therein, the fluid passages having an inlet and an outlet;
- b) a plurality of vaporizing surfaces disposed in the fluid passages;
- c) a heating member disposed adjacent the body; and
- d) a liquid injection member disposed in the inlet of the fluid passages to deliver the one or more liquids onto the plurality of the vaporizing surfaces.

73. The apparatus of claim 72 further comprising a carrier gas passage disposed around the liquid injection member.

74. The apparatus of claim 73 wherein the plurality of vaporizing surfaces define a labyrinth through the body.

75. The apparatus of claim 72 wherein the body is comprised of a first and a second block, each block defining a complimentary set of vaporizing surfaces to define the one or more fluid passages when mounted adjacent to one another.

76. The apparatus of claim 75 wherein the heating member is disposed on each block.

77. The apparatus of claim 76 wherein the liquid injection member is a capillary tube.

78. The apparatus of claim 74 wherein the plurality of vaporizing surfaces comprise a plurality of fins disposed in the fluid passages to form a labyrinth.

79. The apparatus of claim 74 wherein the plurality of vaporizing surfaces comprise a corrugated surface.

80. The apparatus of claim 77 further comprising a thermocouple disposed adjacent the inlet of the fluid passages.

81. The apparatus of claim 72 further comprising a liquid injection member housing having one or more passages formed therethrough, the housing connectable to the main body of the vaporizer.

82. The apparatus of claim 81 wherein the liquid injection member is disposed in

one of the passages formed in the housing.

83. The apparatus of claim 82 further comprising a gas channel formed in the passage around the liquid injection member.

84. The apparatus of claim 81 wherein the housing further comprises a thermal choke.

85. The apparatus of claim 84 wherein a tip of the liquid injection tube is disposed in the inlet of the one or more fluid passages.

86. The apparatus of claim 85 wherein the temperature of the tip of the liquid injection tube is controlled by disposing the tube through the housing.

87. The apparatus of claim 86 further comprising a gas inlet passage disposed around the liquid injection member.

88. The apparatus of claim 87 wherein the body is comprised of a first and a second block, each block defining a complimentary set of vaporizing surfaces to define the one or more fluid passages when mounted adjacent to one another.

89. The apparatus of claim 88 wherein the heating member is disposed on each block.

90. The apparatus of claim 89 wherein the liquid injection member is a capillary tube.

91. The apparatus of claim 90 wherein the plurality of vaporizing surfaces comprise a plurality of fins disposed in the fluid passages to form a labyrinth.

92. The apparatus of claim 90 wherein the plurality of vaporizing surfaces comprise

a corrugated surface.

93. The apparatus of claim 90 further comprising a thermocouple disposed adjacent the inlet of the fluid passages.

94. The apparatus of claim 90 further comprising one or more liquid injection lines connected to the liquid injection member.

95. The apparatus of claim 93 wherein the liquid injection lines have a low coefficient of friction.

96. The apparatus of claim 94 wherein the liquid injection lines are comprised of PTFE.

97. The apparatus of claim 96 wherein the liquid injection tube is adapted to provide stability of liquid fluid flow at flow rates less than about 100mg/min.

98. The apparatus of claim 77 wherein the capillary tube is adapted to deliver one or more liquids onto the vaporizing surfaces at a supersonic velocity at a liquid injection flow rate of less than about 100mg/min.

99. The apparatus of claim 98 wherein the capillary tube comprises an upper inner diameter of at least about 5 mils and a lower inner diameter of at least 1 mil.

100. A pumping assembly for a processing chamber, comprising:

a) housing mountable to the chamber, the housing defining one or more ports therein;

b) a removable temperature controlled liner disposed in the housing and mountable to the housing;

c) a pumping system fluidically mounted to at least one of the ports formed in the housing.

101. The pumping assembly of claim 100 wherein the liner is mounted to a first end

of the housing and the chamber mounts to a second end of the housing.

102. The pumping assembly of claim 101 wherein the pumping system comprises a first pump connected to a first exhaust port of the housing and a second pump connected to a second exhaust port of the housing.

103. The pumping assembly of claim 102 wherein the second pump is selectively communicable with the housing via a valve disposed upstream from the pump.

104. The pumping assembly of claim 103 wherein the second pump is a high vacuum pump.

105. The pumping assembly of claim 102 further comprising a cold trap disposed upstream from the pump.

106. The pumping assembly of claim 100 wherein the liner comprises one or more channels formed in the liner along the length thereof.

107. The pumping assembly of claim 106 further comprising one or more heating elements disposed in the liner in the channels.

108. The pumping assembly of claim 107 wherein the liner further comprises one or more thermocouples disposed in the liner in the channels.

109. The pumping assembly of claim 107 wherein the liner comprises a plurality of heating elements connected in parallel.

110. The pumping assembly of claim 105 wherein the cold trap comprises:

- a) a housing;
- b) a body disposed in the housing having one or more fluid passages disposed through one end thereof and connected to a central gas passage and one or

more coolant channels formed adjacent the fluid passages; and

- c) an exhaust port fluidically connected with the central passage.

111. The pumping assembly of claim 107 wherein the liner further comprises one or more guide members disposed on at least one end of the liner.

112. The pumping assembly of claim 111 wherein the guide members comprise an insert made of a wear resistant material.

113. The pumping assembly of claim 112 wherein the material is comprised of Teflon.

114. A gas feedthrough for a processing chamber, comprising:

- a) a conduit having an inlet and an outlet, the conduit defining a shoulder for forming a seal with the chamber;
- b) a heating element disposed along the length of the conduit.

115. The gas feedthrough of claim 114 further comprising a thermocouple disposed adjacent the heating element.

116. The gas feedthrough of claim 114 wherein the heating element is a cable heater disposed around the conduit.

117. The gas feedthrough of claim 114 wherein the gas inlet mounts a fitting to connect the inlet to a fluid source.

118. The gas feedthrough of claim 117 wherein gas outlet comprises an upper surface having a channel formed adjacent thereto for supporting a seal.

119. The gas feedthrough of claim 118 wherein the conduit is threaded on one end thereof for securing the feedthrough in the chamber.

120. The gas feedthrough of claim 112 wherein the conduit comprises:

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- a) an outer shell having an upper portion defining the mounting shoulder;
- b) a central tube forming a fluid passageway and having the heating element disposed adjacent thereto; and
- c) a void formed at least partially between the outer shell and the central tube.

121. The gas feedthrough of claim 120 wherein the central tube mounts on an upper surface of the outer shell.

122. The gas feedthrough of claim 121 wherein the central tube comprises an upper mounting surface for forming a seal with a second surface.

123. The gas feedthrough of claim 122 wherein the upper mounting surface defines a sealing groove therein.

124. The gas feedthrough of claim 123 wherein the outer shell further comprises a lower threaded portion for receiving a nut thereon to secure the outer shell in a passage formed therefor.

125. The gas feedthrough of claim 124 wherein the outer shell and the central tube are welded at the upper surface of the outer shell.

126. The gas feedthrough of claim 125 wherein the outer shell further comprises a seal groove formed on the mounting shoulder.

127. The gas feedthrough of claim 126 further comprising a connector disposed on the lower end of the central tube for connecting a gas source.

128. An apparatus for delivering fluids to a processing chamber, comprising:
a gas manifold defining at least a first and a second gas passage therein, the first and second gas passages having an inlet and an outlet, and wherein the outlet of the second fluid passage is disposed in the outlet of the first fluid passage.

129. The apparatus of claim 128 further comprising a restrictive passage formed between the first and second fluid passage to deliver one or more gases from the outlet of the second gas passage into the outlet of the first gas passage.

130. The apparatus of claim 129 wherein the restrictive passage is sized to deliver a fluid flown through the second fluid passage into the outlet of the first fluid passage at a high velocity.

131. The apparatus of claim 130 further comprising a gas distribution assembly mounted on the gas manifold and connected to the outlet of the first fluid passage, the gas distribution plate comprising a first and a second gas distributing plate.

132. The apparatus of claim 129 further comprising a conductance guide mounted on the gas manifold.

133. The apparatus of claim 132 further comprising a gas distribution plate mounted on the conductance guide.

134. The apparatus of claim 133 wherein the conductance guide is an annular plate mounted on the gas manifold.

135. The apparatus of claim 128 wherein the gas manifold comprises a chamber mounting surface for sealably connecting the at least first and second gas passages with one or more gas passages formed in a chamber and adapted to deliver one or more gases into the gas manifold.

136. The apparatus of claim 135 wherein the chamber mounting surface and the conductance guide define a slot therebetween for mounting the gas distribution plate.

137. The apparatus of claim 136 wherein the gas distribution plate further comprises a first and a second gas distributing surface.

138. A method of depositing a film, comprising:

- a) delivering one or more liquid precursors to a vaporizer;
- b) vaporizing the one or more liquid precursors;
- c) selectively delivering the vaporized precursors through a bypass line connected to an exhaust system to stabilize the vaporization process;
- d) selectively delivering the vaporized precursors to a deposition chamber to deposit a film on a substrate; and
- e) selectively delivering the vaporized precursors through the bypass line connected to the exhaust system during a substrate transfer operation.

139. The method of claim 138 wherein the vaporized precursors are selectively delivered by a valve disposed downstream from the vaporizer.

140. The method of claim 139 wherein the vaporized precursors selectively delivered to the exhaust system are filtered by one or more filters.

141. The method of claim 140 wherein the one or more filters comprise one or more

cold traps.

142. The method of claim 138 wherein the vaporizer is maintained at a temperature of at least about 100°C.

143. A system for delivering a liquid, comprising:

a) one or more pressurized ampoules having an outlet and containing one or more liquids;

b) a valve connected to the outlet of the one or more ampoules, the valve adapted to have a zero dead volume.

144. The system of claim 143 wherein an inert gas is delivered to the ampoule to provide pressure therein.

145. The system of claim 144 further comprising a liquid delivery connected at a valve to the outlet of the ampoule.

146. The system of claim 145 wherein the valve is a zero dead volume valve.

147. The system of claim 146 further comprising a solvent line connected to the liquid delivery line at a valve to selectively deliver a solvent to the liquid delivery line.

148. The system of claim 147 further comprising a purge gas line connected to the liquid delivery line at a valve to selectively deliver a purge gas to the liquid delivery line.

149. The system of claim 148 further comprising a liquid flow controller for selectively delivering one or more liquids to a vaporizer.

150. The system of claim 149 further comprising a pressure gauge disposed on the liquid delivery line.

151. An apparatus for filtering a fluid, comprising:
- a) a housing;
 - b) a filtering member disposable in the housing, the filtering member having one or more temperature controlled fluid passages formed therein.
152. The apparatus of claim 151 wherein the filtering member further comprises a body member defining a chamber and one or more fluid passages connected one end of the body member and the chamber.
153. The apparatus of claim 152 wherein the one or more fluid passages are sized and adapted to filter material from the fluid and to prevent clogging of the passages.
154. The apparatus of claim 153 wherein the one or more passages are arranged and sized to provide high conductance.
155. A apparatus for lining a process zone, comprising:
- a) a removable insert sized and adapted for insertion into the process zone;
 - b) a heating member disposed in the insert; and
 - c) an electrical connection for coupling power to the heating member.
156. The apparatus of claim 155 wherein the insert comprises an annular shield having one or more supports disposed thereon.
157. The apparatus of claim 156 wherein the insert is comprised of a material selected from the group comprising a metal, a ceramic or quartz.
158. The apparatus of claim 156 wherein the insert is comprised of aluminum.

VAPORIZATION AND DEPOSITION APPARATUS AND PROCESS

BACKGROUND OF THE INVENTION

Field of the Invention

The invention relates to an apparatus and process for the vaporization of liquid precursors and deposition of a film on a suitable substrate. Particularly contemplated is an apparatus and process for the deposition of a metal-oxide film, such as a barium strontium titanate (BST) film, on a silicon wafer to make integrated circuit capacitors useful in high capacity dynamic memory modules.

Background of the Invention

The increasing density of integrated circuits (ICs) is driving the need for materials with high dielectric constants to be used in electrical devices such as capacitors for forming 256 Mbit and 1 Gbit DRAMs. Capacitors containing high-dielectric-constant materials, such as organometallic compounds, usually have much larger capacitance densities than standard $\text{SiO}_2\text{-Si}_3\text{N}_4\text{-SiO}_2$ stack capacitors making them the materials of choice in IC fabrication.

One organometallic compound of increasing interest as a material for use in ultra large scale integrated (ULSI) DRAMs is BST due to its high capacitance. Deposition techniques used in the past to deposit BST include RF magnetron sputtering, laser ablation, sol-gel processing, and chemical vapor deposition (CVD) of metal organic materials.

A liquid source BST CVD process entails atomizing a compound, vaporizing the atomized compound, depositing the vaporized compound on a heated substrate and annealing the deposited film. This process requires control over the liquid precursors and gases from introduction from an ampoule into a liquid delivery system through vaporization and ultimately to the surface of the substrate where it is deposited. The goal is to achieve a repeatable process which deposits a film of uniform thickness under the effects of a controlled temperature and pressure environment. The goal has not been satisfactorily achieved because the precursors are finicky and the deposition equipment requires a complex design.

For example, one difficulty encountered is that the delivery of liquid precursors has typically required positive displacement pumps. Pumps can become clogged and

require replacement if the precursors deposit on the surfaces of the pumping system. In addition, use of positive displacement pumps becomes problematic when the delivery lines or the vaporizer become clogged with deposits because the pump can rupture the pressure seals or continue to operate until the pressure relief valves on the pump are tripped. Either result may require maintenance and repair and over time repair and replacement of pumps becomes very expensive and increases the cost of ownership of the equipment.

Another difficulty encountered is that BST precursors have a narrow range of vaporization between decomposition at higher temperatures and condensation at lower temperatures thereby requiring temperature controlled flow paths from the vaporizer into the chamber and through the exhaust system. In addition, the liquid precursors tend to form deposits in the delivery lines and valves disposed throughout the system.

Another difficulty encountered is the difficulty or lack of efficiency in vaporizing the liquid precursors. Typically, only a portion of the liquid precursors are vaporized due to low conductance in the vaporizer, thereby inhibiting deposition rates and resulting in processes which are not consistently repeatable. In addition, known vaporizers used in CVD processes incorporate narrow passages which eventually become clogged during use and are not adapted for continuous flow processes which can be stabilized. This too results in a reduction in vaporization efficiency of the liquid precursors and negatively affects process repeatability and deposition rate. Still further, known vaporizers lack temperature controlled surfaces and the ability to maintain liquid precursors at a low temperature prior to injection into the vaporizer. This results in deposition of material in the injection lines in the vaporizer and premature condensation or unwanted decomposition of the precursors.

Still another difficulty encountered in the deposition of BST is that the deposition process is performed at elevated substrate temperatures, preferably in the range of about 400-750° C and the annealing process is performed at substrate temperatures in the range of about 550°-850° C. These high temperature requirements impose demands on the chambers used in the deposition process. For example, elastomeric O-rings are typically used to seal the deposition chamber and are not generally made of materials that will resist temperatures in excess of about 100° C for many fabrication cycles. Seal failure may result in loss of proper chamber pressure as

well as contamination of the process chemistry and the system components, thereby resulting in defective film formation on the wafer. In addition, it is necessary to prevent temperature fluctuations of system components which result from thermal conduction. Loss of heat due to thermal conduction causes temperature gradients across the surface of the substrate resulting in decreased uniformity in film thickness and also increases the power demands required of the system to maintain the high temperature environment in the chamber.

There is a need, therefore, for a deposition apparatus and method which can deliver liquid precursors to a vaporizer, efficiently vaporize the precursors, deliver the vaporized precursors to the surface of a substrate and exhaust the system while maintaining elevated temperatures in the chamber, preventing unwanted condensation or decomposition of precursors along the pathway and avoiding temperature gradients in the system. It would be preferable if the system were adapted for rapid cleaning and continuous flow operation.

Summary of the Invention

In one aspect of the invention, a deposition chamber is provided for depositing BST and other materials which require vaporization, especially low volatility precursors which are transported as a liquid to a vaporizer to be converted to vapor phase and which must be transported at elevated temperatures to prevent unwanted condensation on chamber components. Preferably, the internal surfaces of the chamber are maintainable at a suitable temperature above ambient, e.g., 200-300°C, to prevent decomposition and/or condensation of vaporized material on the chamber and related gas flow surfaces. The chamber comprises a series of heated temperature controlled internal liners which are configured for rapid removal, cleaning and/or replacement and preferably are made of a material having a thermal coefficient of expansion close to that of the deposition material. The chamber also preferably includes features that protect chamber seals, e.g., elastomeric O-rings, from the deleterious effects of high temperatures generated during fabrication of electrical devices, such as capacitors useful for ULSI DRAMs. This concept is generally referred to as a "hot reactor" within a "cool reactor".

The invention also provides a vaporizing apparatus having large vapor

passageways for high conductance to prevent clogging for consistently mixing and efficiently vaporizing liquid precursor components, and delivering the vaporized material to the deposition chamber with negligible decomposition and condensation of the gas in the vaporizer and gas delivery lines. Preferably, the apparatus increases vaporizing efficiency by providing increased surface area and a tortuous pathway with wide passages to reduce the likelihood of fouling or clogging typically associated with existing vaporizers.

The invention also provides a system for delivering liquid source components to the vaporizer without requiring high pressure pumps and which provides gravity assisted feed and cleaning of the lines. Pressurized ampoules deliver the liquid precursors into the vaporizer. The ampoules are preferably chargeable up to about 500psi using an inert gas such as argon. The use of pressurized ampoules eliminates the need for high pressure pumps to deliver the liquid precursors into the vaporizer.

The invention also provides a liquid and gas plumbing system which allows access into the chamber without requiring that any hard plumbing lines be disrupted. Preferably, vaporized materials are delivered from the vaporizer through the chamber body and into a gas distribution assembly in the lid which includes a mixing gas manifold and a gas distribution plate. The chamber body and the mixing gas manifold of the lid sealably connect gas passages disposed therein on engagement.

Still further, the invention provides a flushable system which can operate in a continuous flow mode or a discontinuous mode where it is turned off during the transfer of substrates into or out of the chamber. One or more zero dead volume valves and a gravity feed system enable the system to cycle between a deposition mode where the liquid precursors are vaporized and delivered to the chamber and a substrate transfer mode where solvent is delivered to the lines and valves to flush the system to prevent build-up of material in the liquid/vapor delivery lines. The solvent can be routed through the liquid delivery lines, the vaporizer and through a bypass line and into a disposal system. In addition, the system may continually vaporize precursors but deliver the vaporized material to the exhaust system through a bypass line. This enables stabilization of the process over a number of substrates through optimization and maintenance of the vaporization process.

Still further, the invention provides a pumping system for the chamber which

can maintain chamber pressures at a high vacuum state and which has a plumbing system configured to protect the pumps from deposition of deposits therein. In one aspect of the invention, cold traps are disposed upstream from an exhaust pump to remove vaporized gas from the system. In another aspect of the invention, a high vacuum pump is selectively isolated from the exhaust passage by a suitable valve such as a gate valve to enable selective communication with the high vacuum pump in the absence of process gases.

The chemical vapor deposition system of the present invention is characterized by its use in the manufacture of capacitor films of consistently high quality, with significantly reduced maintenance times and easier maintenance and capability for depositing CVD films at high rates with less particle generation. The net result is a fabrication process with enhanced efficiency and economy.

Brief Description of the Figures

Figure 1 is a perspective view of a chamber system of the present invention;

Figure 2 is cross sectional view of a chamber of the present invention;

Figure 3a is a cross sectional view of a heated gas delivery line through the chamber wall;

Figure 3b is a cross sectional view of a gas delivery line through the chamber wall;

Figure 4 cross sectional view of an alternative embodiment of a chamber and associated purge gas pumping nose assembly of the present invention;

Figure 5 is a substantially bottom perspective view of a chamber liner;

Figure 6 is a cross sectional view of a chamber liner showing a connector for a resistive heating element;

Figure 7 is a top view of a lid of the present invention;

Figure 8 is a partial cross sectional view of a gas manifold;

Figure 9 is a top view of a gas manifold;

Figure 10 is a cross sectional view of a gas manifold;

Figure 11 is a side view of a heated nose liner;

Figure 12 is an end view of a mounting flange for the nose liner;

Figure 13 is a perspective view of a cold trap filter member;

Figure 14 is a perspective view of a chamber and vaporizer module;

Figure 15 is a cross sectional view of a vaporizer of the present invention;

Figure 16 is a top schematic view of a fin structure of the vaporizer of the present invention;

Figure 17 is a cross sectional view of an alternative embodiment of a vaporizer;

Figure 18 is a schematic of a liquid delivery system;

Figure 19 is a perspective view of a zero dead volume valve;

Figure 20 is a cross sectional view of a zero dead volume valve; and

Figures 21-27 are graphical representations of characteristics of a preferred CVD BST 200mm process.

Detailed Description of the Invention

The present invention is directed to a liquid delivery chemical vapor deposition (CVD) system useful in depositing thin metal-oxide films as well as other films requiring vaporization of precursor liquids. The system has particular application for the fabrication of metal-oxide dielectrics useful in making capacitors used in ULSI DRAMs as well as a number of other electrical devices. In general, devices that can be made with the present system are those characterized by having one or more layers of insulating, dielectric or electrode material deposited on a substrate.

Figure 1 is a perspective view of a CVD system 10 of the present invention. The system 10 generally includes a chamber body 12, a heated lid assembly 14, an integrated vaporizer module 16 and an exhaust/pumping system 18. Not shown in this figure, but a feature of the invention, is a liquid delivery system for supplying the liquid precursors to the vaporizer module. The size and dimensions of the system are dictated by the size and shape of the workpiece on which processes of the present invention are performed. A preferred embodiment of the invention will be described herein with reference to a chamber adapted to process a circular substrate, such as a 200mm silicon wafer.

The inventors have recognized that deposition layer uniformity can be enhanced, and system maintenance can be reduced, if substantially all of the system components (other than the substrate and substrate heater) which "see" the process chemistry are substantially maintained at an ideal isothermal system temperature (*e.g.*,

250° C \pm 5° for BST). The deposition chamber incorporates several active and passive thermal control systems, including features for minimizing temperature gradients that can be created as a result of the relatively high temperature of the substrate and the substrate support member. The deposition chamber also includes thermal control features which serve to protect a main chamber seal by cooling it below the ideal isothermal system temperature. Other similar thermal control features maintain a cover enclosing the chamber lid at a relatively safe temperature to prevent burn injuries. Cooling is achieved without inducing significant temperature fluctuations and gradients in the system components exposed to the system chemistry, and without excessive cooling and heating power losses.

The Deposition Chamber

Figure 2 is a cross sectional view of one embodiment of a deposition chamber showing the chamber body 12 supporting a heated lid assembly 14. The chamber body 12 defines an inner annular processing region 20 defined on the perimeter by an inner wall 22. A substrate support member 24 extends through the bottom of the chamber and defines the lower end of the processing region 20. A gas distribution plate 26 mounted on the lid forms the upper limit of the processing region 20. The chamber body 12 and the lid assembly 14 are preferably made of a rigid material such as aluminum, stainless steel or combinations thereof. The chamber body 12 also defines a pumping port for purging the remains of the deposition vapor once it has been delivered over the substrate. A generally U-shaped passage surrounding the gas distribution assembly forms a pumping channel # through which gases are drawn into the exhaust system.

The substrate support member 24 may comprise a metal, *e.g.*, aluminum, with a resistive heating element attached thereto or embedded therein. Alternatively, the support member may comprise a ceramic block and embedded ground plate which generates heat when subjected to RF energy emitted by an adjacent electrode. A suitable substrate support member and related lift assembly is shown and described in co-pending U.S. Patent Application entitled "Self Aligning Lift Mechanism," filed on July 14, 1997, and is incorporated herein by reference. This substrate support member is available from Applied Materials, Inc. of Santa Clara, California under the model

name CxZ Heater.

The substrate support member generally is movable up and down on a central elevator shaft 30 to move a substrate between a deposition position adjacent the gas distribution plate 26 and a substrate insertion/removal position below a slit valve formed through the chamber body. The entry point of the shaft into the chamber is sealed with a collapsible bellows (not shown). The substrate is lifted from or placed on a robot blade by a set of lifting pins 32 slidably retained in a set of four passageways 34 extending through the substrate support member 24. Directly below each of the pins is a lifting plate 36 which moves the pins vertically within the chamber to allow a substrate to be lifted off or placed on a robot blade which is moved into the chamber through the slit valve opening (not shown).

The chamber body 12 defines one or more passages 38 for receiving a heated gas delivery feedthrough 40 having an inlet 42 and an outlet 44 to deliver one or more precursor gases into the gas distribution plate 26 mounted on the lid assembly 14. The passage 38 defines an upper and a lower end of differing diameters to form a shoulder 58 where the upper and lower ends meet. The gas outlet 44 is fluidically connected to a mixing gas manifold 46 which includes at least a first gas passage 48 to deliver a gas(es) into the gas distribution plate 26. An O-ring seal 50, preferably made of Teflon with a stainless steel c-spring, is located around the outlet 44 on the upper chamber wall to provide a sealing connection between the gas delivery feedthrough 40 and the gas manifold 46. Figure 7 is a top view of a lid assembly showing the mixing gas manifold in phantom. One or more oxidizer gas passages 52, similar to passage 38, are also formed in the chamber body 12 adjacent the passage 38 for receiving an oxidizer gas delivery feedthrough which can be heated if desired to deliver one or more oxidizer gases through the chamber wall to the mixing gas manifold 46. A gas passage 54 is formed in the mixing gas manifold 46 to deliver the oxidizer gas to a mixing point 56 located in the gas manifold adjacent the entry port into the gas distribution plate 26. A restrictive passage 37 connects the end of the oxidizer gas passage 54 to the end of the vaporized gas passage 48 to provide high velocity delivery as well as mixing of the gas mixture upstream from the gas distribution plate 26.

Figure 3a is a cross sectional view showing a heated vapor gas delivery feedthrough 40 disposed in the annular passage 38 formed through the chamber wall.

The passage includes a shoulder 58 disposed on the upper end of the passage and includes an O-ring seal 60. The feedthrough preferably includes an outer conduit 41 and an inner conduit 45 disposed within the outer conduit. The outer conduit includes a mounting shoulder 43 which is mounted on shoulder 58 of the passage. The outer conduit also includes a lower end having threads thereon for receiving a lock nut to secure the feedthrough in a sealing position within the passage 38 against the shoulder 58 and O-ring seal 60. The inner conduit 45 defines an upper mounting surface 49 for forming a seal with the lid assembly at O-ring seal 50 and also includes a flange 62 on its lower end for mating with the bottom of the chamber body. A cable type heater 64, or other suitable heater, is disposed in intimate contact with the inner conduit of the feedthrough to heat the feedthrough to a desired temperature. A radiation shield 65 is disposed over the heater to prevent thermal radiation from heating the outer conduit 41. A power lead 67 extends from the lower end of the feedthrough and is connected to a suitable power source to heat the feedthrough. A thermocouple 66 is inserted or otherwise disposed in the heated feedthrough 40 to monitor the temperature thereof. The feedthrough is mounted in the passage and secured therein using a screw type connector or other suitable connector.

The upper wall 47 of the outer conduit 41 is thinned and sized to define a gap between its outer surface and the inner wall of the chamber body to provide a heat choke adjacent the O-ring seal 60. O-ring 50 is preferably a hot O-ring which can withstand temperatures of about 250° C. The thin wall minimizes heat conduction down to the shoulder 58 to protect O-ring seal 60. By minimizing heat conduction, less power is required to heat the feedthrough. Additionally, less thermal mass provides better thermal control and faster response for the feedback control. Still further, the heat choke on the outer conduit prevents heat loss from the mixing gas manifold 46 which is directly connected to the insert and which is heated by the lid body. This avoids generation of cold spots along the path of the vaporized gas.

Figure 3b illustrates an embodiment of a gas feedthrough which is not heated. The oxidizer gas(es) are flown through this non-heated feedthrough. However, in applications where a heated oxidizer gas feedthrough is required, one similar to that shown in Figure 3a can be used. The feedthrough of Figure 3b resembles that of Figure 3a except that the cable heater and thermocouple are removed. In addition, the sizes of

the feedthrough may vary depending on the requirements of the process. In one embodiment, the non-heated oxidizer gas feedthrough has a smaller gas passage and the overall dimensions are therefor somewhat smaller.

Figure 4 is a cross sectional view of an alternative embodiment of the present system. A deposition vapor inlet passageway 68 which communicates directly with a vaporizer outlet port may extend axially through the lid body 14. An annular recess surrounding the inlet passageway is formed on a top side of the main lid body.

Referring again to Figure 2, removable deposition chamber liners (which can be used at a number of different locations) facilitate periodic cleaning of the deposition chamber. A liner in accordance with a preferred embodiment of the invention includes an integral or functionally integral (*i.e.*, assembled from one or more components as attached or overlapping units) generally cylindrical liner 28 that covers upper chamber surfaces adjacent the substrate support member 24 and a bottom liner 29 covers the lower chamber wall surfaces below substrate support member. The liner material may be made of a metal, *e.g.*, stainless steel or aluminum, a ceramic material (*e.g.*, Al_2O_3) or quartz, and can be equipped with an active PID controlled heating element which maintains the liner walls substantially at the optimum isothermal system temperature to inhibit both condensation and decomposition of gas vapor on the chamber surfaces. The material from which the liner is made preferably demonstrates chemical resistance to halogens and halogenated *in situ* cleaning compounds, and is preferably not adversely affected by, nor adversely affects, the process chemistry.

Referring again to Figure 2, a chamber liner 28 is preferably disposed adjacent the inner wall 22 of the chamber to provide a removable surface within the chamber which can be easily cleaned and/or replaced. The liner 28 is supported in the chamber on supports 23, preferably three, which are equally spaced around the lower surface of the liner. The supports 23 are sized to minimize the contact area between the chamber liner 28 and the chamber body and thereby minimize heat conduction between the liner and the chamber body. In one embodiment, the liner is heated by radiation from the heated lid and the heated substrate support member. This embodiment is referred to as a passive floating liner. Alternatively, the liner may also include a resistive heater 25 (shown in Figure 5), or other suitable heater, disposed therein so that it can be actively heated and maintained at an ideal isothermal temperature. This actively heated

embodiment is referred to as an active floating liner. Figure 5 is a substantially bottom perspective view of a heated liner 28 having a resistive coil 25 disposed therein and an electrical connector 27 mounted on the lower surface of the liner which houses the electrical connections to the coil.

Figure 6 is a cross sectional view through the active floating liner 28 showing an external housing mounted on the bottom of the chamber through which the electrical connector 27 is disposed. Due to thermal expansion of the liner, accommodation of the expansion is preferably provided or resisted by the external housing mounted on the chamber. The external housing includes a first conduit 29 having a flange 31, 33 disposed on each end thereof for mounting to the bottom of the chamber and for mounting a bellows 35, respectively. The bellows is mounted on one end to the lower end of flange 33 and at the other end to a second conduit 37 at a flange 39 provided therefor. The bellows is sized and adapted to flex to accommodate any thermal expansion in the electrical connector 27 or the liner 28. The electrical connections to the coil extend through the end of the second conduit 37 for easy connection to a power source.

Since the portions of the liner below the substrate support member are typically isolated from the vapor flow, temperature control of these parts is less critical. However, the portion of the liner below the substrate support member may also be actively heated using a resistive type heating element, or other suitable heating member. Preferably, the temperature of the liner both above and below the substrate support member should be maintainable within the optimum isothermal system temperature range, *e.g.*, between about 200°C and 750°C, or other temperature range suitable for the desired deposition material.

A sealing edge ring 160 (shown in Figure 2) is disposed in the chamber and supported on the substrate support member 24 to contact and overlap a circumferential edge of the substrate support member 24. A circumferential rib can be provided on the underside of the ring in order to maintain the ring in an aligned position. The edge ring serves to close-off the annular space 162 between the liner 28 and the substrate support member 24, and thereby substantially reduce the amount of deposition vapor which flows into the lower part of the deposition chamber. In addition, the edge ring acts as a radiation shield. The outer circumferential portion of the gas distribution plate 26

typically extends beyond the diameter of the substrate. The edge ring 160 protects this part of the gas distribution plate 26 from heat directly radiated by the substrate support member. The edge ring 160 is preferably made of a material having a thermal coefficient of expansion similar to that of the deposition material to reduce the possibility of particle generation due to flaking during thermal cycling. In the case of BST, one such edge ring material is titanium. The edge ring of the present invention may be constructed in accordance with the edge ring configuration(s) disclosed in co-pending commonly owned U.S. application Serial No. _____, filed on _____, hereby incorporated by reference in its entirety.

The lid assembly 14 preferably comprises a main body 70 machined or otherwise formed of a metal having a high thermal conductivity, *e.g.*, aluminum. The main lid body defines an annular channel 74 formed around its perimeter to define a thin outer annular wall 76. A support ring 78, preferably made of stainless steel or other thermal insulator, is disposed in the channel to provide structural support for the lid and to prevent thermal conduction to the outer wall 76. The thin outer wall of the body member provides a thermal choke for the base 71 of the lid which is sealed to the chamber body during processing at the O-ring seal 72. The O-ring seal 72 is positioned at a circumferential interface of the chamber body 12 and the lid assembly to maintain a hermetic and vacuum tight seal of the chamber. In order to actively cool the O-ring seal, one or more cooling channels 73 are preferably disposed in the lower lip of the outer wall 76. A heat exchange fluid (*e.g.*, water, ethylene glycol, silicone oil, etc.) circulates through the channel to remove heat at the O-ring seal.

The thermal choke provided by the thin outer wall 76 isolates the O-ring seal 72 between chamber lid 14 and the chamber body 12 from the heat generated by heating elements 80 disposed in the lid. The heat choke provides thermal protection of the O-ring seal 72 by allowing localized active cooling within the channel on top of the O-ring 72, without inducing significant detrimental cooling effects on the other system components. The thin wall 76 presents an effective thermal barrier between the heating elements and the O-ring due to its small cross-sectional area (A) and long length (l).

The upper surface of the main lid body 70 defines a plurality of annular recesses 79, such as spiral grooves, for receipt of a heating element 80 therein. In a preferred embodiment, a heater with a power output of about 6200W is used. However, the

amount of power will vary depending on the lid design and geometry, including material composition of the lid, and the process temperature. Power is delivered to the heating elements through a feedthrough 85 disposed in the lid. The heater is preferably controlled with conventional PID feedback control, based on signals received from a thermocouple 82 positioned or otherwise disposed in the lid. An annular plate 84 serving as a heat shield is mounted on the top of the heating elements. Preferably, the plate 84 is brazed to the lid body to form an integral part of the lid body. A water cooled plate 86 is disposed on or over the plate 84 to provide a controlled mechanism for pulling heat out of the lid for active feedback temperature control.

A cooling channel 100 is preferably formed in top cover plate 86 of the lid assembly 14. Cooling channel 100 removes heat from the lid. In addition, a thermal choke gap, preferably about 25 mils, is used to control the amount of heat removed from the lid during cooling. During deposition of a material such as BST, the substrate will be heated by the substrate support member to a temperature of over 500°C. Heat from the substrate and the substrate support member will radiate onto the gas distribution plate 26 thereby tending to increase its temperature above the optimum isothermal system temperature. By increasing the thermal conduction or transfer between the lid and the gas distribution plate 26, the substrate and substrate support member induced temperature gradients and fluctuations can be reduced. In order to improve heat conductivity between the lid and the gas distribution plate 26, an inert gas (*e.g.*, helium, hydrogen, etc.) is circulated about the annular interface of these elements. The inert gas is introduced into channel 102, which may be circular, spiral or other shape, disposed in the lid. The channel can be formed in the mating annular surface(s) of the gas distribution plate 26 and the main lid body 70 and/or in the cover plate 86. The inert gas can be introduced from the top through the cooling plate or through the bottom of the chamber via a feedthrough connected to the gas manifold. Gas pressure in the channels can be maintained within the range from about 1-100 Torr, preferably within the range of about 1-20 Torr. Due to its high thermal conductivity, the circulating inert gas can improve heat transfer between the lid assembly 14 and the gas distribution plate 26.

The lid assembly, including the heating element, is configured to maintain the

vapor inlet passageway and gas distribution plate at an ideal isothermal system temperature, *e.g.*, $250^{\circ}\text{C} \pm 5^{\circ}$. Passive and active cooling elements are used to maintain the top cover of the lid, and the O-ring seal 72 positioned between the chamber body and the lid assembly, at a substantially lower temperature, *e.g.*, 100°C or lower.

Referring again to Figure 2, the mixing gas manifold 46 includes a central opening 88 which delivers the gases to a blocker plate 90 to initially disperse or distribute the gas(es) over a large area above a face plate 92. Each of the blocker plate and the face plate have a plurality of holes formed therethrough which evenly disperse the gas over the area of the plates 90, 92 and together form the gas distribution plate 26. The face plate 92 delivers the gas uniformly over the area of a substrate positioned on the substrate support member 24. The gas distribution plate 26 and the mixing gas manifold 46 are preferably made of aluminum and are sufficiently thick to allow heat transfer from the gas distribution plate to the temperature controlled lid assembly 14.

With respect to the gas distribution plate assembly, the use of a conventional thin blocker plate 90 with a relatively thicker face plate 92 also serves as a thermal control system. The mixing gas manifold 46 serves as a heated mass whose heat capacity and high thermal conductivity act as a source of thermal inertia resisting temperature variations from the center of gas distribution plate to its periphery. The gas mixing manifold 46 also avoids the effects of gas "channeling" through the material of the plate for providing a more even distribution of gas volume across the substrate surface. While the gas distribution plate is preferably made of aluminum, another thermally conductive material may also be used.

Figure 9 is a top view of a chamber lid showing the heating element 80 and the mixing gas manifold 46. The lower surface of the lid body defines one or more channels 104 for mounting a gas manifold 46. Figure 10 is a partial cross sectional view of a gas manifold 46. The gas manifold 46 includes a gas delivery block 61 which defines one or more gas channels 48, 54 therein having one or more gas inlets 38, 52 on one end and a gas outlet 56 on the other end. The gas outlet 56 serves as a gas inlet of the gas distribution plate 26. An annular conductance restrictor plate 63 is mounted on the lower surface of the gas delivery block to mount the gas distribution plate and prevent gas leakage at the interface between the gas manifold and the gas distribution

plate. The conductance restrictor plate 63 is sized and adapted to define an annular mounting recess 65 to which the gas distribution plate is secured.

A vaporized gas passage 48 and an oxidizer gas passage 54 extend at least partially along the length of the gas manifold from the gas inlets to the gas outlet. The restricting gas passage 37 is disposed between the vapor gas passage and the oxidizer gas passage to optimally mix and deliver the oxidizer gas into the gas outlet and then to the blocker plate and face plate. The restrictive passage 37 delivers the oxidizer gas into the vaporized gas passage at a relatively high velocity to assist in mixing of the gases. Alternatively or additionally, a second set of a vaporized gas passage and an oxidizer gas passage, a carrier gas passage or a cleaning gas passage (to deliver a cleaning gas species from a remote plasma source) may also be provided through the chamber wall to deliver these gases to a second gas manifold.

Figure 4 shows a partial cross sectional view of a pumping system 18 of the present invention. The pumping system 18 includes a pumping nose 106 mounted on the chamber which connects an exhaust passage and related pumps to the chamber. The pumping nose 106 includes a housing 108 which defines a gas passage 110 along its length. The housing supports a removable heated liner 112. Both the housing and the liner define a pair of ports 114, 116, one port 114 connected to a cold trap and exhaust pump and the other port 116 connected to a turbopump 118, or other high vacuum pump, with a gate valve 120 disposed therebetween.

The exhaust liner 112 is shaped and sized to slidably mount within the nose housing 108 and includes a mounting flange 122 on one end to mount to the end of the housing. A second mounting plate 123 is mounted on the first and sealed thereto using an O-ring seal 125. The exhaust liner includes a body 124 which defines a central passage 110 opening into the exhaust manifold in the chamber and the two exit ports, preferably connecting a high vacuum pump and an exhaust pump and related cold traps. Six mounting blocks 126, 128, 130 (three of which are shown) extend at least partially along the length of the central passage to mount four cartridge heaters 132 and two thermocouples 134. The multiple thermocouples provide a back up as well as enable checking temperature uniformity. In one embodiment, the thermocouples extend along the bottom of the liner while the heaters are disposed along the top and in the central portion of the liner. However, other configurations such as heaters on the top and

bottom and thermocouples in the middle or heaters on the bottom and middle and thermocouples on the top are contemplated by the present invention. The heaters are preferably connected in parallel and two connections are provided on the mounting flange of the liner for easy connection to a power source. A cap may be mounted over the mounting plates when removed from the system so that the exhaust liner can be easily cleaned without the risk of jeopardizing the electrical connections to the heaters. The cap can be sealed to the second mounting plate 123 using an O-ring seal or other suitable seal. Also, a handle is preferably mounted on the second mounting plate to facilitate easy removal of the exhaust liner from the nose and submersion in a cleaning bath. Preferably, the second mounting plate 123 includes quick connects for the heaters and the thermocouple cables. Figure 12 is a front view of the second mounting flange 123 showing the heater and thermocouple connections and positions.

Figure 11 is a cross sectional view of an exhaust liner 112. The end of the liner adjacent mounting flange 122 includes a thin walled portion 136 around its circumference which acts as a thermal choke. The thermal choke ensures that an O-ring disposed between the mounting plate 122 and the exhaust housing is not subjected to elevated temperatures. Additionally, the thermal choke regulates the amount of heat transferred to the housing thereby minimizing (*i.e.*, optimizing) the amount of power required to heat the liner. The end proximate the chamber is curved to match the curvilinear contour of the inner wall of the exhaust manifold. Teflon screws 138 are inserted at the chamber of the exhaust liner on at least the bottom and/or the sidewalls of the exhaust liner, preferably both, to provide a smooth surface on which the liner can slide on insertion into or removal from the housing to prevent scratching of the nose liner and/or housing. Teflon is preferred because it can withstand 250°C temperatures, it does not outgas unwanted contaminants and is compatible with various aggressive cleaning solutions. However, screws or plugs formed of other materials possessing these characteristics can be used effectively.

Referring to Figure 1, a turbopump 118, or other high vacuum pump, is mounted to an outlet port 116 of the pumping nose. A gate valve 120 is disposed between the turbopump and the nose to enable selective communication of the turbopump with the chamber. The turbopump enables the vacuum chamber to be

evacuated down to a very low pressure to be compatible with processing platforms such as an Endura® platform available from Applied Materials, Inc. of Santa Clara, California. An exhaust pump such as a roughing pump, dry pump or other pump used in the industry is connected to the chamber at the exhaust port 114 in the nose to pump the chamber during processing. A cold trap 140 is disposed in the conduit connecting the exhaust pump to filter out the deposition material which may be detrimental to the pump. Additionally, a second cold trap 142 is disposed below the first cold trap and is connected to a bypass line from the vaporizer. The bypass line and related cold trap allow the system to operate in a continuous flow made by allowing delivery of vaporized material thereto during wafer transfer.

Figure 13 is a perspective view of a cold trap filter of the present invention. The cold trap is housed in a tubular housing 144 (shown in Figure 1) and includes a filtering member 146 which includes a plurality of cooled passages 148 for condensation of material thereon. The filtering member includes a base portion 147 and a filtering portion 149. The filtering portion 149 includes the plurality of cooled passages 148 formed therein. A water inlet 151 and water outlet 153 are disposed in conduits 155, 157. The gases pass through the filtering member and continue through an exhaust passage disposed in communication with a central portion 150 of the filtering member. This structure enables gases to pass through the filtering portion 149 and on through the exhaust system. The housing 144 mounts a conduit connected to the exhaust pump having an inlet fluidically connected to the central chamber portion 150 so that the gases pass through the cold trap and continue on through the conduit to a disposal system.

A purge gas arrangement provides a purge gas in the lower part of the chamber resulting in a gas shield with upwardly directed flow of gas emanating from the bottom of the chamber. The gas shield strength is adjustable with a mass flow controller. Suitable purge gases include helium, argon and nitrogen, which can be introduced through a purge line 31 and a circular manifold for distributing the gas evenly about the substrate support member and the elevator shaft, within the sealing bellows. The gas flow rate must be set relatively low, *e.g.*, 50sccm, in order to avoid interference with the deposition process. Additionally, the purge gas is directed into the exhaust plenum adjacent the liner and away from the edge of the wafer.

The Vaporizer

Figure 14 is a perspective view showing the vaporizing module 16 mounted adjacent to the chamber 12. A vaporizer 120 is mounted in a vaporizer cabinet 122 and includes an outlet line 124 connected to the inlet into the chamber. Disposed along the outlet line 124 is a first valve 126 which is connected in turn to a bypass line (not shown) extending out through the back of the cabinet 122 and is connected to the exhaust system by a conduit in which the cold trap 142 is disposed (see Figure 1). The bypass line is adapted to deliver both vaporized gas as well as liquid solvent into a cold trap disposed downstream from the valve in preparation of delivering vaporized gas to the chamber or during cleaning of the system. This valve controls delivery of the vaporized material to the chamber or through the cold trap in the exhaust system. A second valve 128 is disposed downstream from the first valve to selectively deliver the vaporized gas into the chamber. The second valve is mounted to the lower portion of the chamber via a rod and washer assembly 130. This assembly enables adjustment of the delivery line as well as the valve in relation to the chamber. The mount generally includes first and second rings 132, 134, respectively, one disposed in the other, to allow rotatable adjustment of an isovalve 128 and the delivery line. The isovalve 128 is mounted to the outer ring 134 via a plurality of rods 136 (four shown here) which are mounted from the ring and include a spring 138 disposed above the upper portion of the rod and the ring 134. The two rings 132, 134 enable rotation of the assembly while the spring and rod arrangement allow vertical adjustment of the assembly to ensure proper alignment of the gas feed line 124 into the chamber through the feedthrough 40. In general, the suspension apparatus provides automatic compensation for thermal expansion/contraction to maintain vacuum seals without the mechanical and thermal stress.

Figure 15 is a cross sectional view of one embodiment of a vaporizer 120 of the present invention. The vaporizer generally includes an injection nozzle 170 disposed through an inlet port 172 of the vaporizer. A concentric passage 174 is disposed about the outer perimeter of the gas injection nozzle 170 to deliver one or more carrier gases to the tip of the nozzle. Preferably, the concentric gas passage is made of PTFE for low friction coefficient and prevention of clogging. The carrier gases are flown

concentrically about the nozzle to prevent liquid droplets from forming on the tip of the nozzle and moving up the outer cylinder of the nozzle. The liquid delivered to the nozzle 170 is carried in a carrier gas, such as argon, and delivered to a central cup-shaped portion 176 of the vaporizer. The cup-shaped portion of the vaporizer forms the central receptacle for the liquid injection stream where vaporization commences. A plurality of fins 178 are disposed around the central cup-shaped portion 176 to define a tortuous path or labyrinth along which vaporization occurs. The fins 178 are spaced from one another in rings which are offset to form the path along which the gas vapor diffuses and are spaced a sufficient distance to reduce the likelihood of clogging. One or more notches 180 are formed in the upper portion of the fins to define a gas flow passage which allows gas flow but which enables the fins to trap any liquid which is not vaporized. This prevents liquids from passing through the vaporizer and into the chamber, as well as enabling a solvent to be delivered into the vaporizer for cleaning without the risk of having the solvent enter the chamber.

Connected with the circular path defined between the outermost circle of fins and internal cylindrical wall surrounding the vaporizer section are a plurality of ports 182 (*e.g.*, six) and associated gas delivery passages converging to a main outlet 184. The arrangement of angled passageways 182 provide a large conductance for shorter resonance time in the vaporizer and also facilitate inspection and cleaning of the vapor flow paths. All of the passages are surrounded by a large solid mass of a lower block 186 and an upper block 188 which are assembled together to form the vaporizer and include a metal-to-metal seal 187. The upper and lower blocks define grooves 190 to mount heating elements. This arrangement helps to ensure that the vaporizing surfaces as well as the vapor are maintained at the optimum isothermal temperature downstream of (as well as in) the main vaporizing section.

The fins 178 of the vaporizing section are preferably formed as integral parts of the upper and lower block, and not as separate attached parts. Thus, in contrast to previous designs, the heating surfaces do not constitute thermally "floating pieces," *i.e.*, pieces whose temperature "floats" or varies (less controllably) in relation to the temperature of one or more separate thermal masses to which the pieces are attached. In a preferred embodiment, respective sets of fins are machined directly into the mating

surfaces of the upper and lower blocks in complimentary configurations which interleaf or interdigitate with each other to form the multi-path, maze-like structure shown in Figure 16. In addition to their vaporizing function, the twists and turns of the pathways of the main vaporizing section also serve to vigorously mix the precursor components and carrier gases and to filter out entrained droplets by impaction as the carrier gas changes direction in the labyrinth.

The radial spacing between the concentrically arranged fins is preferably about 0.5 mm (0.020"), in order to minimize the effects of any deposits which might form. A preferred radial spacing is within the range of about 1-3 mm (0.039-0.118"), and most preferably about 2mm. In a preferred embodiment, the circular fins have a height of about 2-8mm and a density of 2-6 fins per inch (measured in the radial direction). The overall inner diameter of the preferred main vaporizer section is 75mm, and 6 concentric circles are provided with a radial spacing of about 2mm. Each of the circles has four fins; the size and circumferential (end-to-end) spacings of the fins varies directly with the diameters of the circles. Maximum and minimum end-to-end spacings of the fins are 30mm and 2mm, respectively, depending on carrier gas flow, the vaporization behavior of the precursors and thermal stability of the precursors. The spacing between the fins is important to prevent clogging of the vaporizer and to provide maximum surface area on which vaporization can occur. The precursors with low volatility require relatively high conductance and fewer fins. Precursors with low thermal stability require relatively short residence time and therefore high carrier gas flow, a short flow path and fewer fins. Precursors with violent or droplet generating boiling phenomenon require relatively higher numbers of fins to enhance impaction filtering of the droplets.

An important feature of the vaporizer assembly is the arrangement provided for delivery of the liquid precursor mixture to the main vaporizing section, and for mixing the precursor liquid with the carrier gas. The mixture of liquid precursor components is delivered through the nozzle 170 or capillary tube (*e.g.*, 2-20 mil inner diameter) to a point just above the center of the main vaporizing section. The liquid and gas are supplied at a relatively high flow rate, *e.g.*, 10ml/ min. liquid and 100-2000sccm gas, which causes the liquid to exit the capillary tube and enter the main vaporizing section as a jet of liquid and gas with a high nozzle velocity. Importantly, all but a final short

segment of the path of the liquid mixture is kept relatively cool by a thermal choke structure 195 to reduce thermal decomposition of the liquid precursor components prior to vaporization. In particular, the capillary tube extends within a relatively thin tube or neck 192 attached to or forming an integral part of the upper block as shown in Figure 15. Thermal insulation of the capillary tube along this stretch is provided by the relatively thin wall of the neck, *e.g.*, 10-100 mil thickness, as well as by the space between the capillary tube and surrounding internal surface of the neck and by the thermal insulating value of the material. The neck is preferably made of PTFE, stainless steel or other material having a relatively low thermal conductivity. A cooling block 197 and cooling channel 199 enable temperature control of the nozzle 170.

The liquid precursor components are mixed with a concentrically delivered carrier gas as the former is jetted-out of the capillary tube just above the main vaporizing section. The concentrically delivered carrier gas is delivered to this point by a supply line 193 or tube fluidly connected, *e.g.*, with a standard VCR fitting, with an upper part of the internal bore of the neck. The gas flows downwardly within the annular pathway 174 defined between the capillary tube 170 and the internal neck surface. At the level of the nozzle outlet, the carrier gas picks-up the liquid precursor mixture jetting-out of the capillary tube and carries the mixture down into the main vaporizing section 176 where the liquid precursor is vaporized. To allow for optimization of this initial "flash" vaporization, the spacing between the capillary tube nozzle 170 and the main vaporization section 176 is preferably adjustable. For example, the capillary tube can be made axially movable within a web-like centering guide 195 mounted within the central neck bore. Adjustment of the flash vaporization to avoid a liquid droplet "dance on the frying pan" effect is obtained by adjusting the flow rate of the gas and liquid precursor mixture. Any liquid droplets remaining after the initial "flash" vaporization are vaporized as the mixture advances through the tortuous paths of the main vaporizer section, in contact with the heated fins. The resultant deposition gas then passes through the ports and angled feeder passages 182 to the central main passage 184, and through the vaporizer outlet port for direct delivery to the deposition chamber. The mixture is substantially maintained at the predetermined optimum isothermal system temperature (*e.g.*, $250^{\circ}\text{C} \pm 5^{\circ}$). The exit ports are designed for large conductance so that precursor vapors are readily carried

from the vaporizer into the chamber.

The vaporizer operates to vaporize a mixture of precursor components, such as BST, and a carrier gas by providing a main vaporizer section with increased surface area provided along a tortuous pathway which expose the mixture to a large area of evenly heated surfaces and filter out liquid droplets entrained in the flow by droplet impaction during changes in gas flow direction in the tortuous path. The flow velocity, and therefore impaction filtering efficiency, is independently controlled by the flow of an auxiliary argon or other carrier gas input to the vaporizer injection plumbing. In contrast to conventional arrangements, the amount of heating, *e.g.*, vaporizing, power supplied to the mixture is set substantially higher than the level of power actually required to achieve complete vaporization. The amount of power required for complete vaporization is a function of the chemistry of the precursor components and carrier gas, and the flow rate of the mixture. As one example, with a BST flow rate of .10 ml/min and a carrier gas, *e.g.*, Ar, flow rate of 200-300 sccm, the amount of power necessary to heat and completely vaporize the flow is approximately 10W. As will be understood, a metering valve can be used to control the amount of gas flow in direct relation to the flow rate of the liquid precursor component mixture.

In accordance with the invention, the thermal power transferred to the vaporizer is set to be one to two orders of magnitude higher than the 10W required for complete vaporization of the mixture, *i.e.*, between about 100W and 1000W, and preferably 20-30 times higher, *i.e.*, 200-300W. In this manner, the heating power absorbed by the flowing mixture is a small fraction of the heating power which is available. Therefore, the power absorbed by the gas vapor presents an insignificant perturbation in relation to the available heating power, making it possible to substantially maintain an ideal isothermal temperature (*e.g.*, $250^{\circ}\text{C} \pm 5^{\circ}$) of the heating surfaces. In general, depending on the precursor component mixture which is used, the ideal isothermal system temperature will be in the range of about 200-300°C.

Also, the vaporizer body is configured to help ensure the maintenance of an isothermal temperature of the main vaporizing section. Specifically, the heating surfaces are preferably integrally formed in adjoining surfaces of upper and lower blocks of metal, *e.g.*, aluminum or stainless steel. The blocks provide a relatively large

thermal mass for retention and transmission of thermal energy generated by one or a pair of heating elements surrounding the blocks. In a preferred embodiment, the upper and lower blocks are provided as segments of a cylindrical rod and one or a pair of heating elements, such as a cable heater, are wrapped helically about the circumference, and along the lengths, of the rod segments.

As one specific example, the top and bottom cylindrical blocks may each have an outer diameter of 3.5". The top segment may have a length of 1", and the bottom segment a length of 2". The segments may be bolted together by a plurality of bolts, *e.g.*, eight, extending in an axial direction and equally spaced around the perimeter of the blocks. Preferably, the segments are sealed to each other with a known type of high temperature metal-to-metal seal situated in a circular groove provided in one or both of the blocks and surrounding the main vaporizer section. One example of a metal-to-metal seal is the aluminum Delta seal from Helicoflex.

The heating elements preferably deliver a total heating power of between about 1000W and 3000W to the blocks. If separate heaters are used to heat the top and bottom segments, a 1500W bottom heater and a 675 W top heater may be used to provide a total heating power of 2175 W. Helical grooves (not shown) are preferably formed on the outer surface of the blocks and the heating elements are secured in the grooves, *e.g.*, by welding. The heater is controlled to maintain the main vaporizing section at the optimum isothermal temperature by a conventional PID controller. The controller is connected with a thermocouple positioned within one, and preferably both, of the upper and lower segments directly adjacent the heated vaporizing surfaces.

In an alternative embodiment shown in Figure 17, the upper and lower block do not provide interdigitating fins, but rather provide a fin structure 178 is disposed only on the lower block. The upper block defines an upper roof 179 of the vaporizing chamber. The fins 178 are spaced from one another and include passages therethrough to enable flow of vaporized gas through the fin structure and out through the outlets. It is believed that this arrangement enables greater conductance of vaporized gas and to reduce resonance time in the vaporizer.

Applications of the System

Exemplary metal-oxide layers which can be deposited using the present system

may include tantalum pentoxide (Ta_2O_5), a zirconate titanate ($\text{Zr}_x\text{Ti}_y\text{O}_z$), strontium titanate (SrTiO_3), barium strontium titanate (BST), lead zirconate titanate (PZT), lanthanum-doped PZT, bismuth titanate ($\text{Bi}_4\text{Ti}_3\text{O}_{12}$), barium titanate (BaTiO_3), BST, PZT, lanthanum-doped PZT, or the like. Other materials which can be deposited include those materials having a narrow range between vaporization and decomposition.

Substrates used in the present invention include primarily P-type and N-type silicon. Depending on the particular process chemistry and desired end product, other substrate materials may be usable, including other semiconductors, *e.g.*, germanium, diamond, compound semiconductors, *e.g.*, GaAs, InP, Si/Ge, SiC, and ceramics.

The selection of materials for the layers above the circuit element in an integrated circuit device depends on the device that is formed and other layers that a particular layer currently or subsequently contacts. For example, a DRAM requires a high permittivity capacitor, but the metal-oxide dielectric layer does not need to have ferroelectric properties.

Devices that can be made with the present system include, but are not limited to, 64Mbit, 256Mbit, 1Gbit and 4Gbit DRAMs.

The system also has particular application with other liquid precursors which are volatile as well as materials such as copper.

Liquid Delivery System

Figure 18 is a perspective view showing a liquid delivery system 200 of the present invention. The liquid delivery system generally includes a liquid precursor module 202, a solvent module 204 and a vaporizer module 206. In one embodiment, the liquid precursor module 202 includes two pressurized ampoules 208, 210 and a liquid delivery line 212 connected to each ampoule. Valves are disposed along the length of the liquid delivery lines to control flow of liquid from the ampoules to a mixing port and then into the vaporizer. Preferably, zero dead volume valves, which are described below, are used to prevent collection of precursor therein which can compromise the valves as well as negatively affect process stabilization and/or repeatability. The zero dead volume valves enable rapid flushing of precursor from the lines using solvent. Solvent is plumbed to the liquid delivery line by line 214 to flush

the system during maintenance. Additionally, a purge gas line is plumbed to the liquid delivery line to rapidly purge solvent from the line so that the system, including the ampoules, valves and/or LFCs, can be prepared for maintenance in ten (10) to thirty (30) minutes. The valving is designed so that when necessary, solvent can be introduced into the liquid delivery line upstream from the mixing port to flush the line through a bypass line 218 and out through a recovery system which includes a cold trap and exhaust manifold.

The ampoules are designed to deliver the liquid precursors at high pressure, *e.g.*, up to 500 psi, without having to rely on high pressure pumps, *i.e.*, no high cycle mechanical pump with rubbing parts exposed to precursors. To provide the pressure, an inert gas such as argon is charged into the ampoules at a pressure of about 90 psi through line 220. A liquid outlet line 222 is disposed in the ampoule so that as the inert gas, *e.g.*, argon, is delivered to the ampoule and the appropriate valves are opened, the liquid is forced out through the outlet through a suitable valve and into the liquid delivery line.

The delivery line 212 is connected from each ampoule to the vaporizer. A first zero dead volume valve is disposed on the outlet of the ampoule to control delivery of the liquid to the delivery line 212. The valve is preferably a three-way valve connecting the bypass line 218 and the liquid delivery line 212. The bypass line 218 in turn is connected to a cold trap and an exhaust manifold (not shown). A high pressure gauge 224 and a LFC 226 are disposed downstream from a valve 228 introducing the solvent and the purge gas. The LFC controls delivery of the liquid to the mixing port 230 connected between the liquid precursor delivery lines. A low pressure gauge 232 is disposed on the bypass line 218 to monitor pressure in the line so that completion of the maintenance routine can be determined.

The liquid precursor delivery lines 212 deliver liquid precursors into the mixing port 230 upstream from the vaporizer 120. A solvent delivery line 234 also delivers a solvent into the liquid delivery line downstream from the mixing port where the liquid precursors and the solvent are mixed and delivered into the vaporizer. At the vaporizer, a carrier gas line 236 delivers a carrier gas into the delivery line to carry the liquid precursors and the solvent into the vaporizer through the capillary tube or nozzle. In addition, a concentric carrier gas line 238 delivers a carrier gas around the nozzle or

injection tip to ensure that even a small amount of liquid is delivered to the vaporizing surfaces. The delivery line from the mixing port and into the vaporizer is preferably made of a material having a low coefficient of friction, such as Teflon PTFE, and does not hang up in the line. This feature assists in the delivery of small volumes of liquid precursor.

The solvent module 204 includes one or more chargeable ampoules similar to the liquid precursor ampoules. Preferably, there are two solvent ampoules 240, 242 and two liquid precursor ampoules 208, 210. The liquid precursor ampoules can deliver two separate precursors which can be mixed at the mixing port or can deliver the same precursor together or alternatively.

The liquid precursor ampoules are designed with a slotted/sculptured bottom to draw the liquid downwardly in the ampule so that the liquid may (1) be detected at very low levels and (2) be drawn out of the ampule even at low levels. This is particularly important in dealing with expensive liquids which are preferably not wasted. In addition, the ampoules include an ultrasonic detector for discerning the volume of liquid in the ampoule even at low levels so that continuous processing may be achieved.

Figure 19 is a perspective view of a zero dead volume valve. The valve includes a liquid precursor inlet 252 and a solvent inlet 254 and a single outlet 256. The solvent is routed through the solvent inlet through a solvent control actuator 258 and into the liquid precursor control actuator 260. A plunger 262 controls entry of the solvent into and consequently out of the solvent control actuator as shown in Figure 20. The liquid precursor is routed through the precursor inlet 252 and into precursor control actuator 260 when the plunger 264 in the actuator is in the open position. When the plunger is in the closed position, the precursor is prevented from entering the actuator and is flushed out of the valve by the plunger and by flow of solvent through the valve. The solvent is able to enter the precursor control actuator 260 whether the plunger is in the open or closed position to enable solvent purge of the valve as shown in Figure 20. The plunger is contoured to seal the liquid precursor inlet while enabling solvent flow into the actuator. Continuous solvent flow allows the system to be continuously purged with solvent when the liquid precursors are shut off.

Additionally, a single actuator valve is disposed on the outlets of the ampoules to control delivery of liquid precursor and to prevent clogging in the actuator. Also, the

two way valves are preferably disposed on the downstream side of the liquid flow controllers in the vaporizer panel.

The delivery tubes are preferably made of a material such as Teflon to promote frictionless fluid flow therein to prevent clogging and deposition along the path of the tubes. It has been learned that Teflon provides a better conduit for materials such as the barium, strontium and titanium precursor liquids used in the deposition of BST.

The plumbing system is designed to enable rapid flushing of the lines and valves during routine maintenance. Additionally, the is adapted to enable sequential shutdown of each of the valves as well as to deliver an automatic flush of a controlled amount of solvent through the vaporizer and the delivery lines in case of a power outage. This safety feature ensures that during uncontrolled power outages, the system will not be subject to clogging.

The delivery system may also comprise a bubbler system where a carrier gas such as argon can be bubbled through a solvent to suppress premature solvent evaporation from the precursor, thereby ensuring the precursor liquid will not be dried out en route to the vaporizer.

In situ liquid flow controllers and piezoelectric control valves are also used to maintain heightened control over the system. The high pressure gauges present on precursor and solvent lines as well as vacuum gauges on the vacuum manifolds are used to measure whether chemicals remain in the lines. These gauges are also used for on board leak integrity measurements.

A preferred embodiment of the present invention includes a liquid CVD component delivery system having two pressurized ampoules of liquid CVD component and a related LFC, such as a needle valve, which operates without sliding seals and can be used at pressures of less than 250 psi. Two solvent ampoules deliver solvent into the liquid delivery lines for cleaning and maintenance as well as into the mixing port during processing.

BST Process

The vapor desired for use in the deposition process is shown as a mix of first and second vaporized liquid precursors combined in predetermined mass or molar proportions. For use in deposition of BST, the first liquid precursor is preferably one of

a mixture of Ba and Sr polyamine compounds in a suitable solvent such as butyl acetate. The preferred mixtures combine bis(tetra methyl heptandionate) barium penta methyl diethylene triamine, commonly known as Ba PMDET (tmhd)₂, and bis(tetra methyl heptandionate) strontium penta methyl diethylene triamine, commonly known as Sr PMDET (tmhd)₂, or, in the alternative, bis(tetra methyl heptandionate) barium tetraglyme, commonly known as Ba (tmhd)₂ tetraglyme, and bis(tetra methyl heptandionate) strontium tetraglyme, commonly known as Sr (tmhd)₂ tetraglyme. The second liquid precursor is preferably bis(tetra methyl heptandionate) bis isopropanide titanium, commonly known as Ti (I-pr-o)(tmhd)₂, or other titanium metal organic sources, such as Ti(tBuO)₂(tmhd)₂. The molar ratio between the combined metals in the first liquid precursor and the second liquid precursor is preferably about 2:1:4 Ba:Sr:Ti. The molar ratio can vary from about 2:1:2 to about 2:1:8.

The BST process mixes the vaporized first and second liquid precursors with an oxidizing gas such as oxygen, N₂O, O₃ or combinations thereof, at a temperature above the vaporization temperature of the precursors and below a temperature which degrades the components. The process is very sensitive to changes in temperature of the substrate, solvent content of the liquid precursors, and concentration of the oxidizer in the combined gases. Increasing the wafer temperature increases the deposition rate, reducing the solvent content of the liquid precursors reduces the haze of the films, and controlling the oxidizer flow rate controls the roughness of the film and crystalline phase.

Figure 21 is a graph of the deposition rate versus heater temperature in a CVD BST 200 mm substrate process of a preferred embodiment of the present invention. A heater temperature of 600°C provides a high deposition rate without substantial degradation of the precursors. The heater temperature can vary from about 300°C to about 800°C. For the examples shown in Figure 21, the first precursor was a mixture of Ba PMDET (tmhd)₂ and Sr PMDET (tmhd)₂ in butyl acetate having a molar ratio of Ba:Sr of 2:1. The second precursor was Ti (I-pr-o) (tmhd)₂ in butyl acetate which provides a molar ratio of Ba:Sr:Ti of 2:1:4. The substrate was a Pt/SiO₂/Si substrate. A deposition rate of 220 Å/minute was achieved at a heater temperature of 600°C using a total liquid flow rate of the precursors at 200mg/m and a process gas flow rate of 1500 sccm (that is, a combination of oxygen, nitrogen and argon, each at a flow rate of 500

sccm). A vaporizer according to the present invention was also used, wherein the vaporizer lines for the precursors were maintained at 240°C.

As shown by Figure 21, the deposition rate increases an average of 1.3 Å/min for each 1°C increase in the heater temperature, showing that there is a strong sensitivity to temperature. A deposition rate of over 200 Å/minute indicates high vaporizer efficiency.

A high deposition rate of 150 Å/minute process can provide a high quality film having good uniformity within the wafer and from wafer to wafer. A heater temperature of 550°C provided a wafer temperature of 470°C and a deposition rate of 160 Å/minute. Satisfactory electrical properties have been obtained with a deposition rate as high as 169 Å/minute.

Figure 22 is a graph of the log of the deposition rate shown in Figure 21 versus $1/T$ divided by the temperature of the wafer heater in 1000°K. As shown in Figure 22, there are two distinct regimes with respect to the deposition rate. Mass transport of the precursors limits the deposition process where the log of the deposition rate is around 5 or greater. The deposition process is surface reaction limited where the log of the deposition rate is about 4 or smaller. The transition between these two regimes takes place at about 550°C, or about a 470°C wafer temperature. A 500-550°C regime provides good uniformity for step coverage optimization. Results were obtained by simply varying the temperature and observing the deposition rate. The significance is that the PMDETA precursors are permitting high decomposition rates and a well behaved reaction mechanism with a simple single transition in rate controlling reaction at a 470°C wafer temperature.

Figure 23 demonstrates the high quality films produced by this invention using the process conditions described for Figure 21. Three deposition runs were made over a two day period to deposit films having thicknesses of 1150 Å, 550 Å, and 550 Å. The uniformity of the wafers is shown by a graph of measured titanium concentration (mole%) versus wafer number as well as measured deposition rate (Å/min) versus wafer number. This graph shows that wafer-to-wafer deposition rates are uniform and meet the desired target rate. This graph also illustrates a rapid change in Ti concentration for the first several wafers in each run which presents an opportunity for improvement of

the process. This graph further shows that the composition is not very sensitive to deposition time as had been expected. Figure 23 shows reasonably tight process control which can be further improved through the use of 3-part barium, strontium and titanium mixtures and by running the vaporizer in continuous flow mode.

Figure 24 is a table of a Ti sensitivity test with a wafer heater temperature of plus or minus 0.5°C during deposition. This figure shows the mole % for Ti, Ba, and Sr for two separate wafers. Si Prime means non-previously used silicon. Si Recl means reclaimed silicon from other processes. Pt /ox 1 is an oxidized silicon substrate with platinum sputtered thereon using physical vapor deposition techniques. Pt /ox 2 is an oxidized platinum substrate further characterized as electron beam platinum. The matrix results show that plus or minus 0.5°C during deposition yields the best repeatability in 5 out of six cases. In addition, the matrix results show that the substrate is coated with about 8-10 mole % more Ti on Pt versus Si, and about 2 mole % Ti for 20% Ti(I-pr-O) demonstrating substrate sensitivity.

Figure 25 is a graph of the composition sensitivity of Ti, Ba and Sr to temperature in the CVD BST process described for Figure 21, where concentration (mole %) of Ti, Ba and Sr are each plotted versus wafer heater temperature. At about 600°C, the Ti concentration of the deposited film increases 1 mole % for each increase in heater temperature of 2°C. At about 600°C, the Ba concentration of the deposited film decreases 1 mole % for each increase in heater temperature of 2.5°C. At about 600°C, the Sr concentration of the deposited film decreases 1 mole % for each increase in heater temperature of 10°C demonstrating strong temperature dependence. This temperature dependence is substantially reduced at a 680°C heater temperature.

In the preferred embodiment of the present invention, it is critical to maintain the heater in the 600-750°C range to optimize electrical properties and for optimal step coverage. It has been found that certain chemicals used in a certain temperature range produce good results. Specifically, polyamine based Ba and Sr precursors and Ti (I-pr-o) are the precursors that are believed to work the best in the present invention. A wafer control of plus or minus 0.50°C is preferred for the above-mentioned precursors.

Example 1

A preferred process according to the present invention deposits a BST film on a 200 mm wafer mounted on a heated substrate holder spaced 550 mils from a gas distribution showerhead or face plate. The deposition occurs at 1.7 Torr with a wafer temperature of 600°C and the following flow rates. The first precursor was 33 mg/min to 200 mg/min of a mixture of Ba PMDET (tmhd)₂ and Sr PMDET (tmhd)₂ in butyl acetate having a molar ratio of Ba:Sr of 2:1. The second precursor was 17 mg/min to 77 mg/min of Ti (I-pr-o) (tmhd)₂ in butyl acetate which provides a molar ratio of Ba:Sr:Ti of 2:1:4. The substrate was a Pt/SiO₂/Si. A deposition rate of 40 to 160 Å/minute is achieved using process gas flow rate of 2900 sccm (that is, a combination of O₂ at 500 sccm, N₂O at 500 sccm, Ar_A at 1500 sccm, and Ar_B at approximately 900 sccm). A vaporizer according to the present invention was also used, wherein the vaporizer lines for the precursors were maintained at 240°C.

Example 2

In another example, a process according to the present invention deposits a BST film on a 200 mm wafer mounted on a heated substrate holder spaced 550 mils from a gas distribution showerhead. The deposition occurs at 7 Torr with a heater temperature of about 680°C and the following flow rates. The first precursor was 33 mg/min to 200 mg/min of a mixture of Ba PMDET (tmhd)₂ and Sr PMDET (tmhd)₂ in butyl acetate having a molar ratio of Ba:Sr of 2:1. The second precursor was 17 mg/min to 77 mg/min of Ti (I-pr-o) (tmhd)₂ in butyl acetate which provides a molar ratio of Ba:Sr:Ti of 2:1:4. The substrate was a Pt/SiO₂/Si. A deposition rate of 151 Å/minute was achieved using process gas flow rate of 1300 sccm (that is, a combination of O₂ at 250 sccm, N₂O at 250 sccm, Ar_A at 500 sccm, and Ar_B at approximately 300 sccm). A vaporizer according to the present invention was also used, wherein the vaporizer lines for the precursors were maintained at 240°C. As shown in Figures 26 and 27, a two mixture process showed repeatable results over a twenty five wafer run.

Example 3

In another example, the system was cleaned using acetone as a solvent. The acetone used was not dried. A deposition process according to that described in Example 1 was then performed. A 2x increase in the deposition rate was observed

indicating that residual acetone solvent stabilized the precursors on delivery to the substrate and consequently resulted in the higher deposition rate. It is believed that the acetone stabilizes the precursors through hydrogen bonding so that more precursor is delivered to the substrate surface for reaction.

Example 4

It is believed that use of a solvent such as acetone during the deposition process will stabilize the precursors and result in a higher deposition rate.

While the foregoing is directed to a preferred embodiment of the invention, other and further embodiments of the invention may be devised without departing from the basic scope thereof, and the scope thereof is determined by the claims which follow.

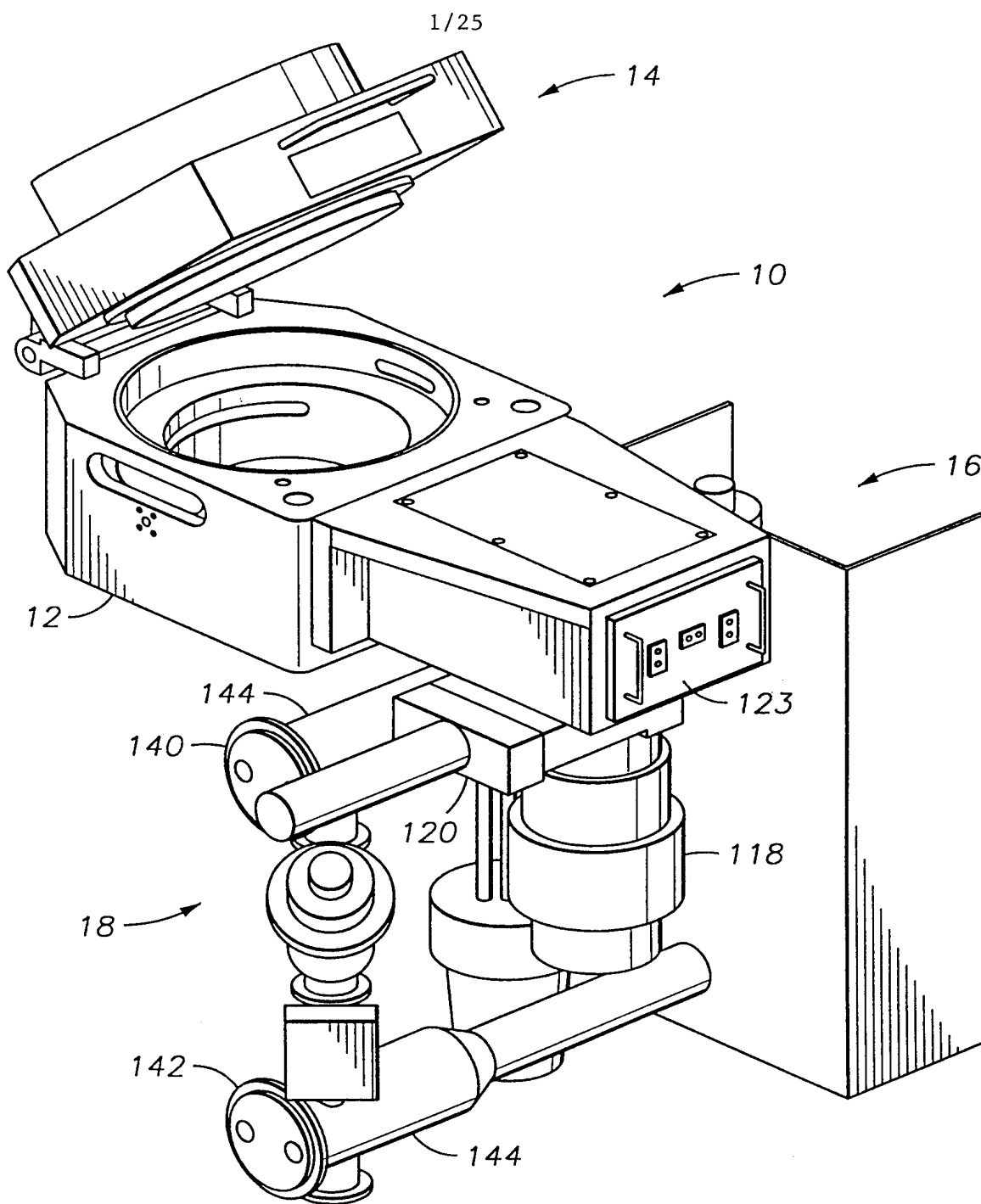


FIG. 1

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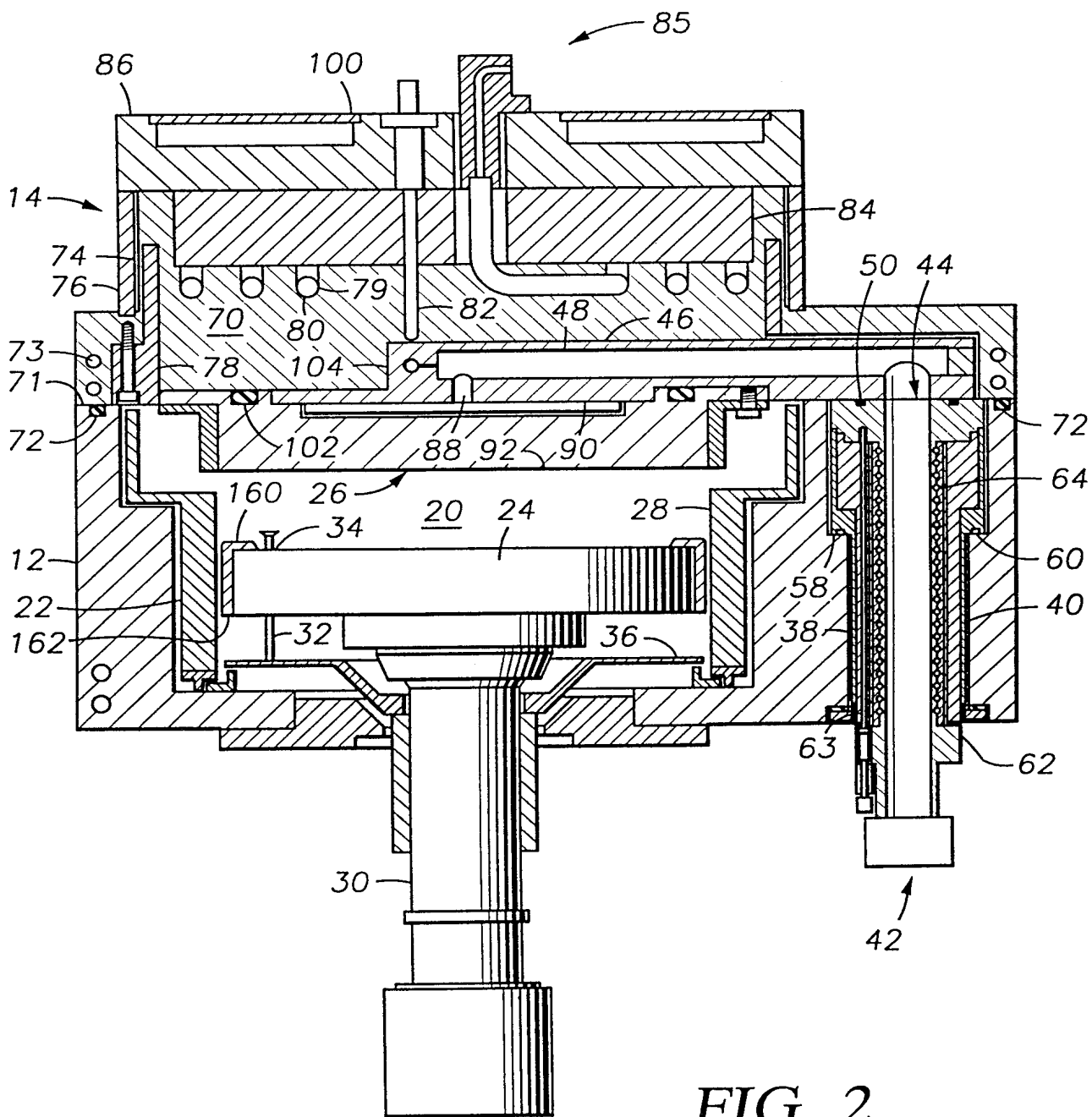
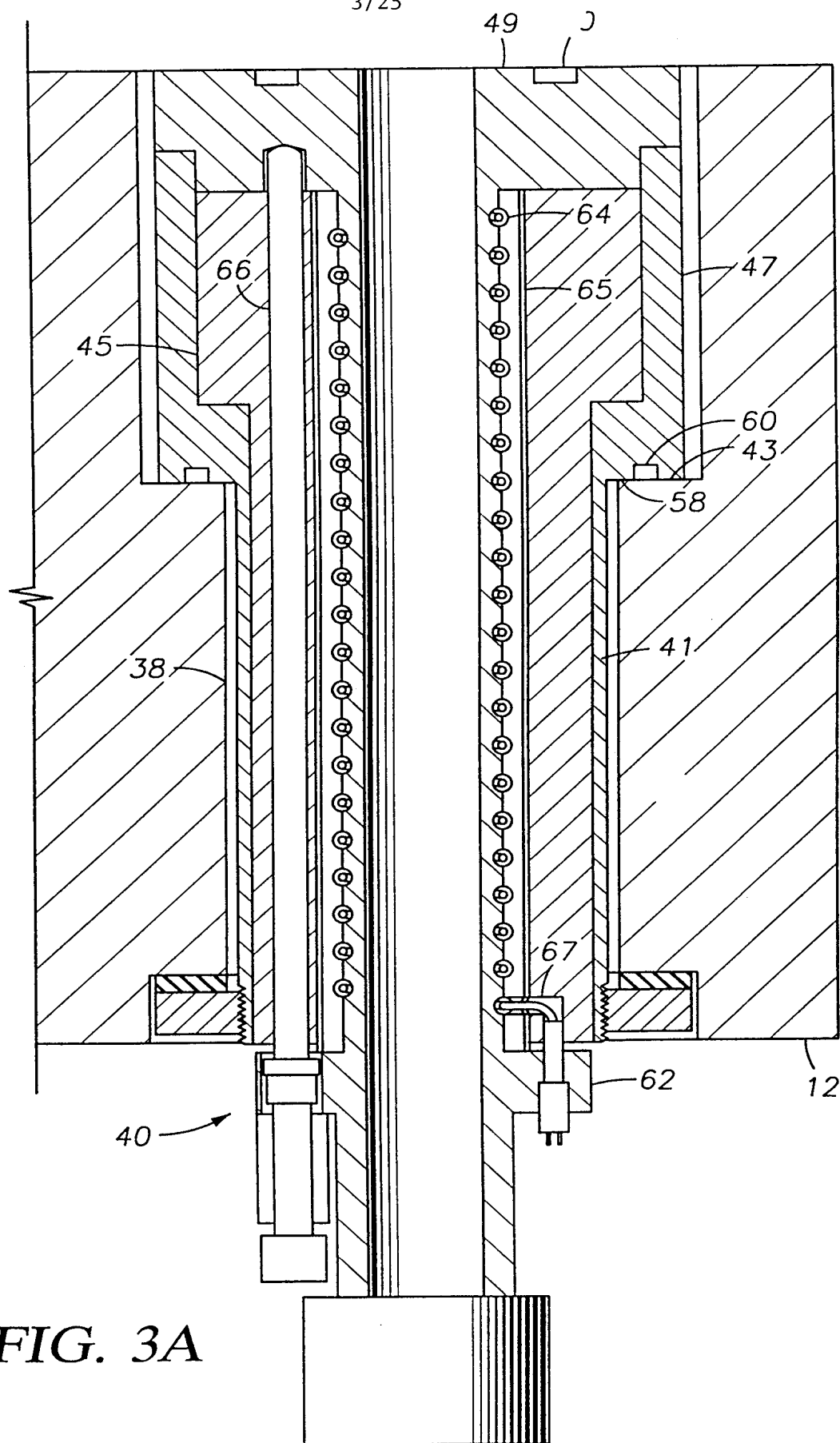
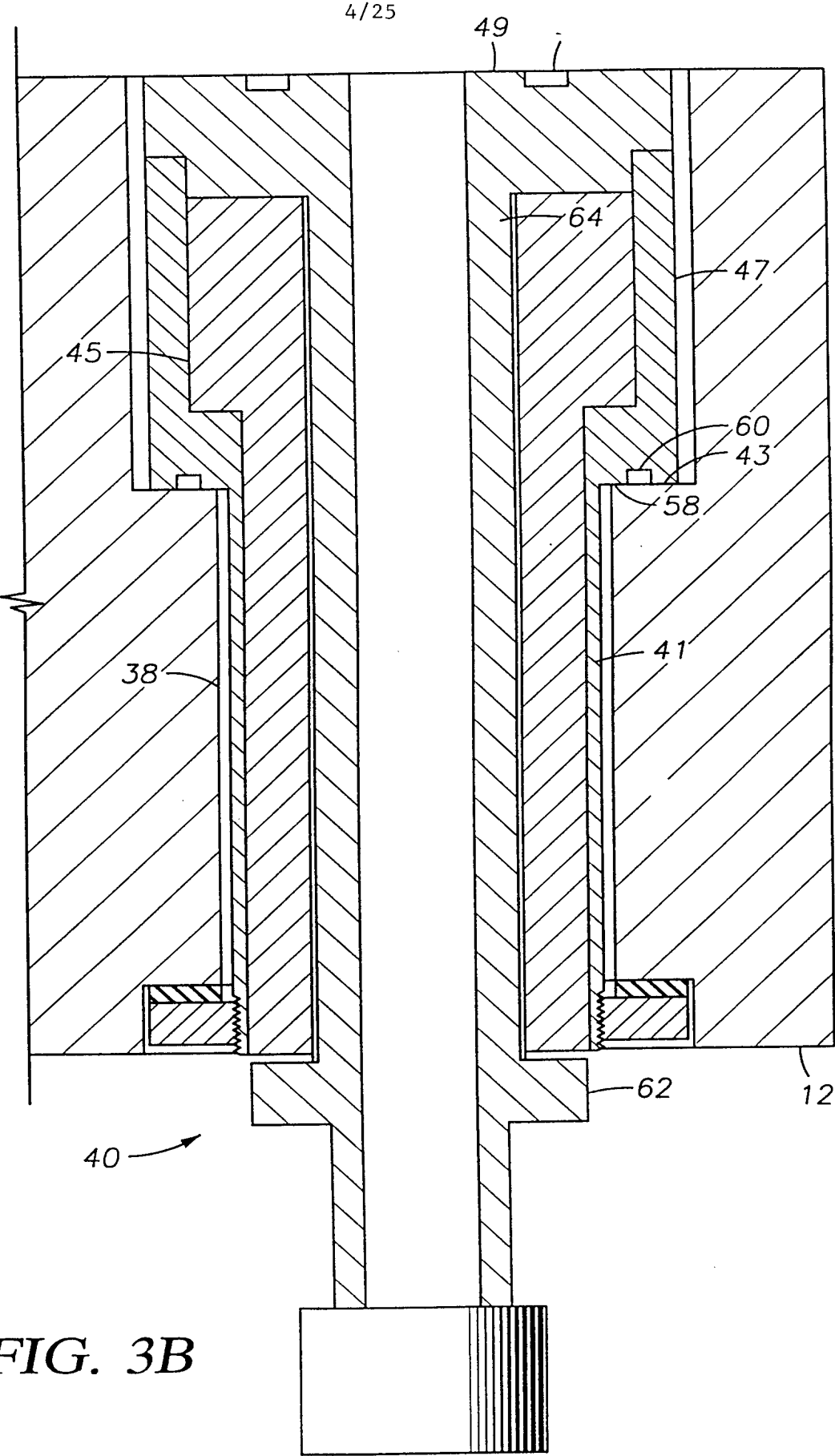


FIG. 2

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**FIG. 3A**



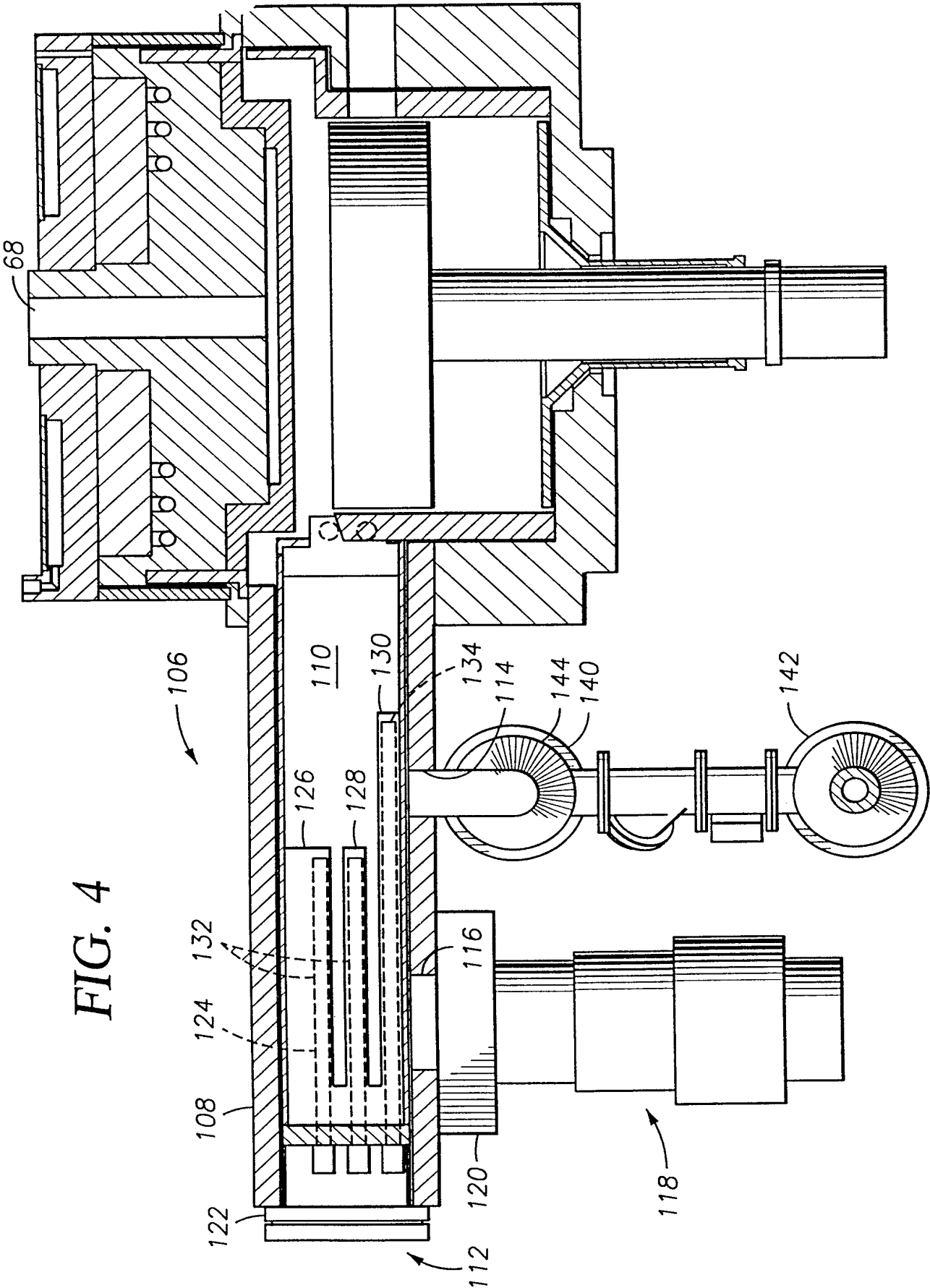
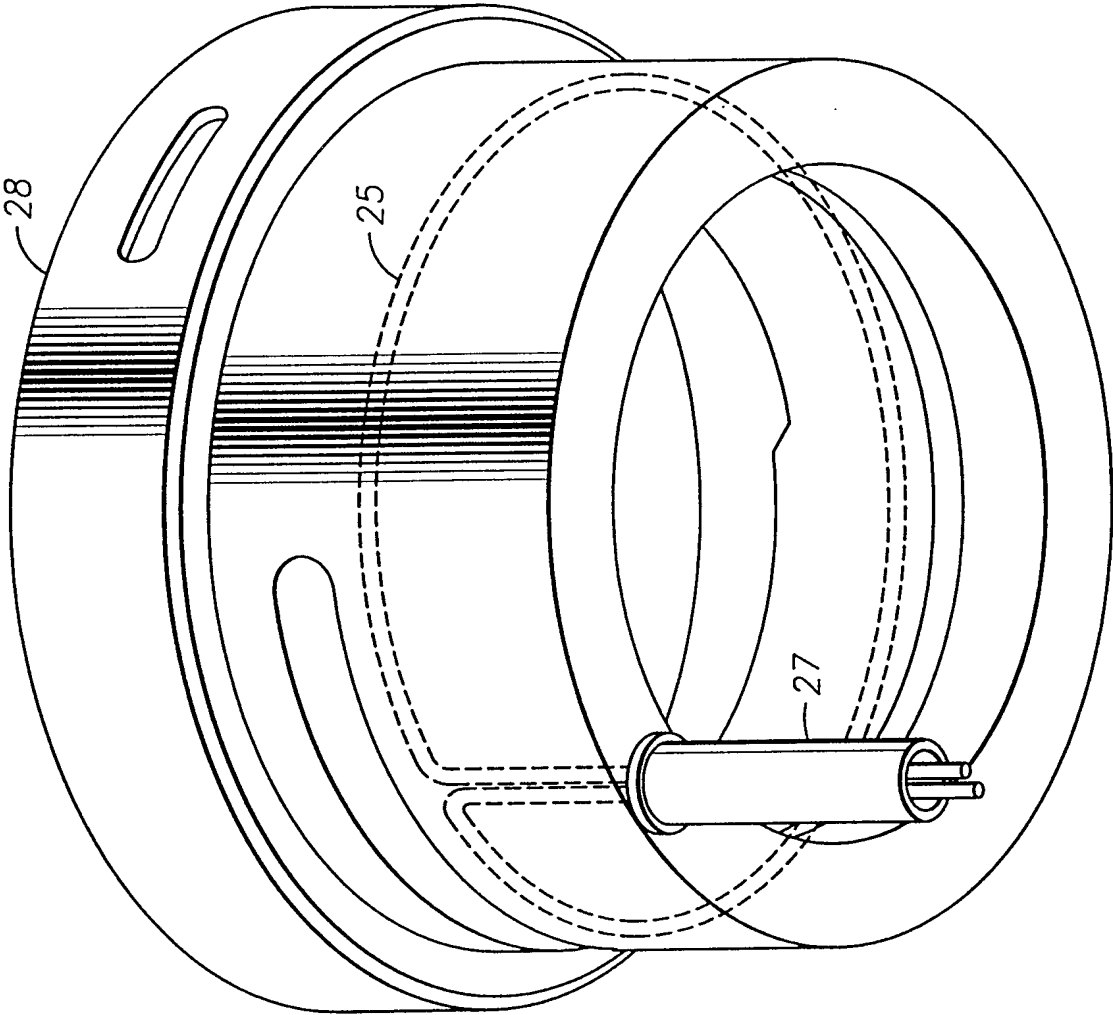


FIG. 4

FIG. 5



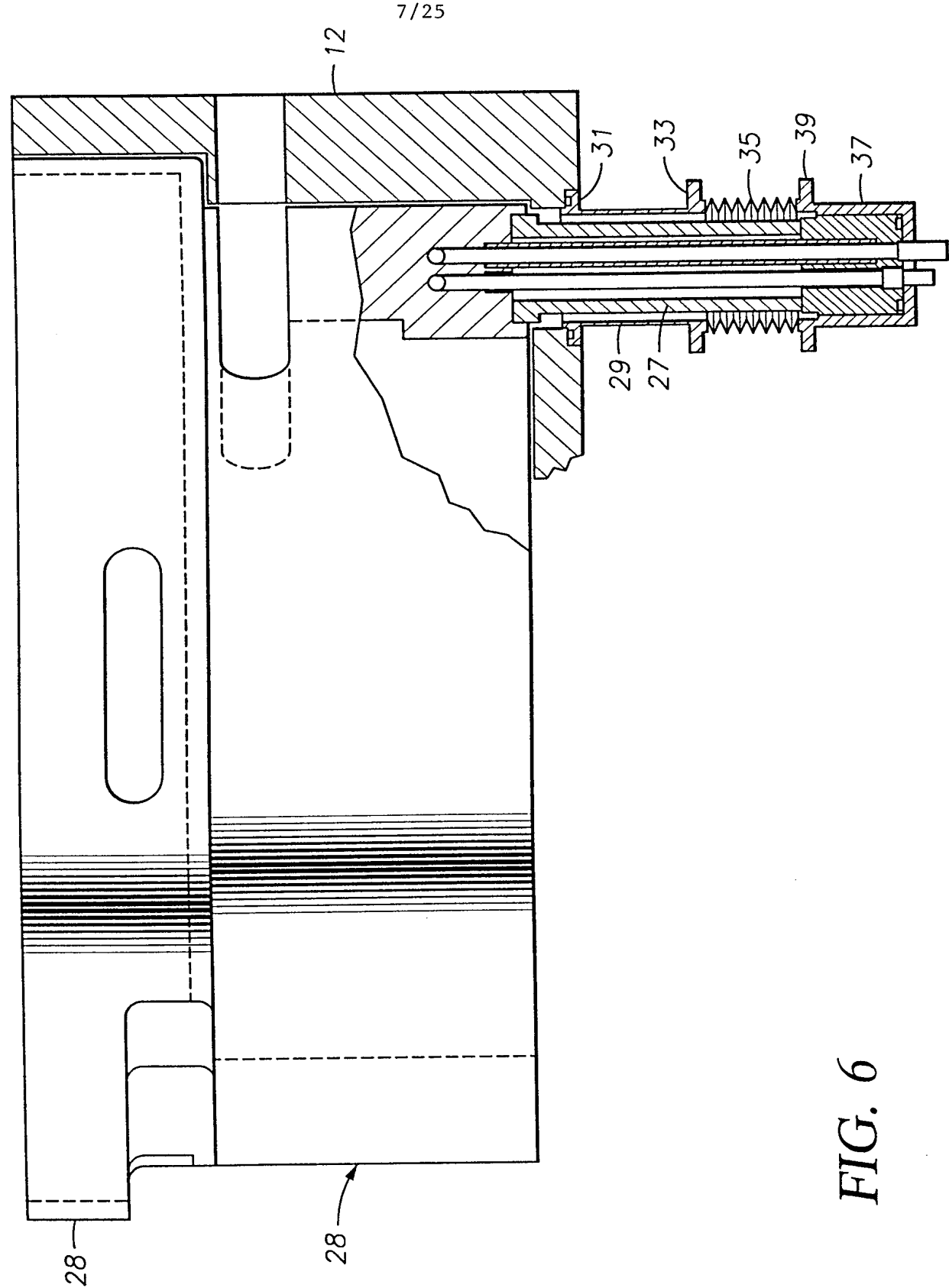


FIG. 6

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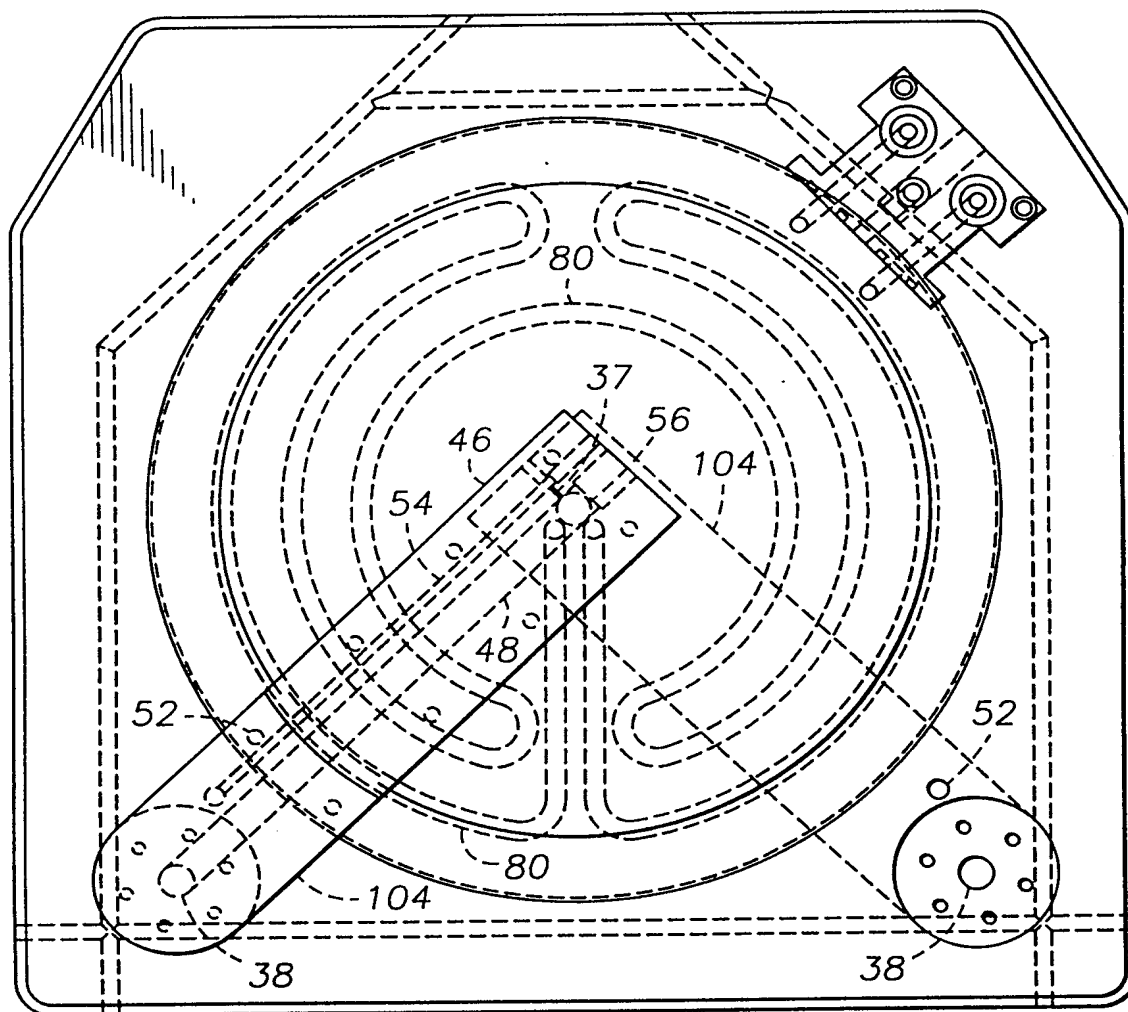


FIG. 7

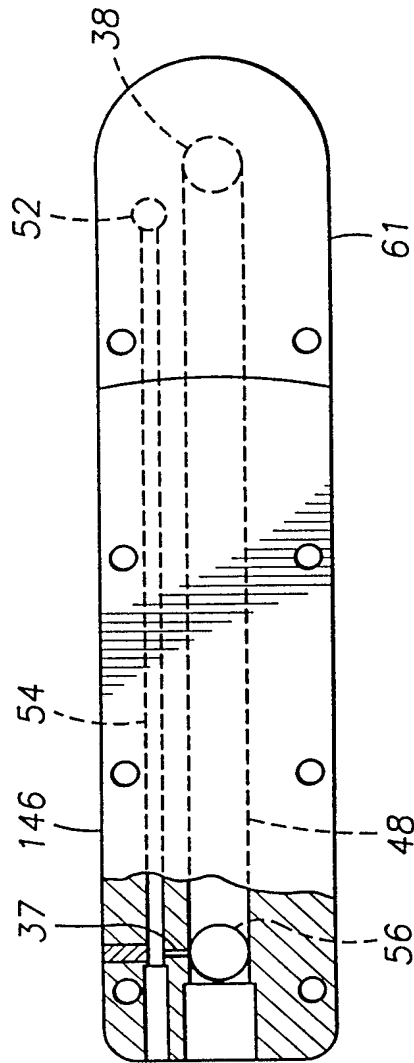


FIG. 8

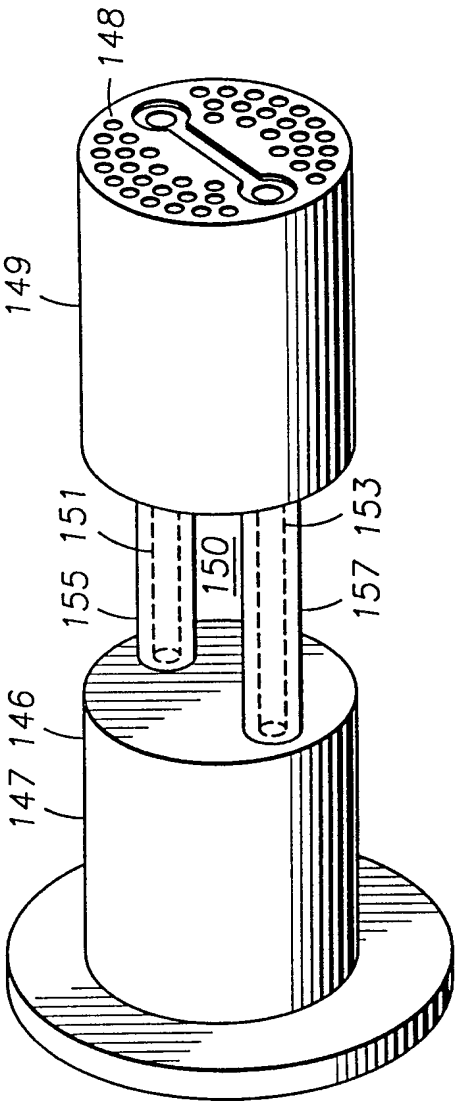


FIG. 13

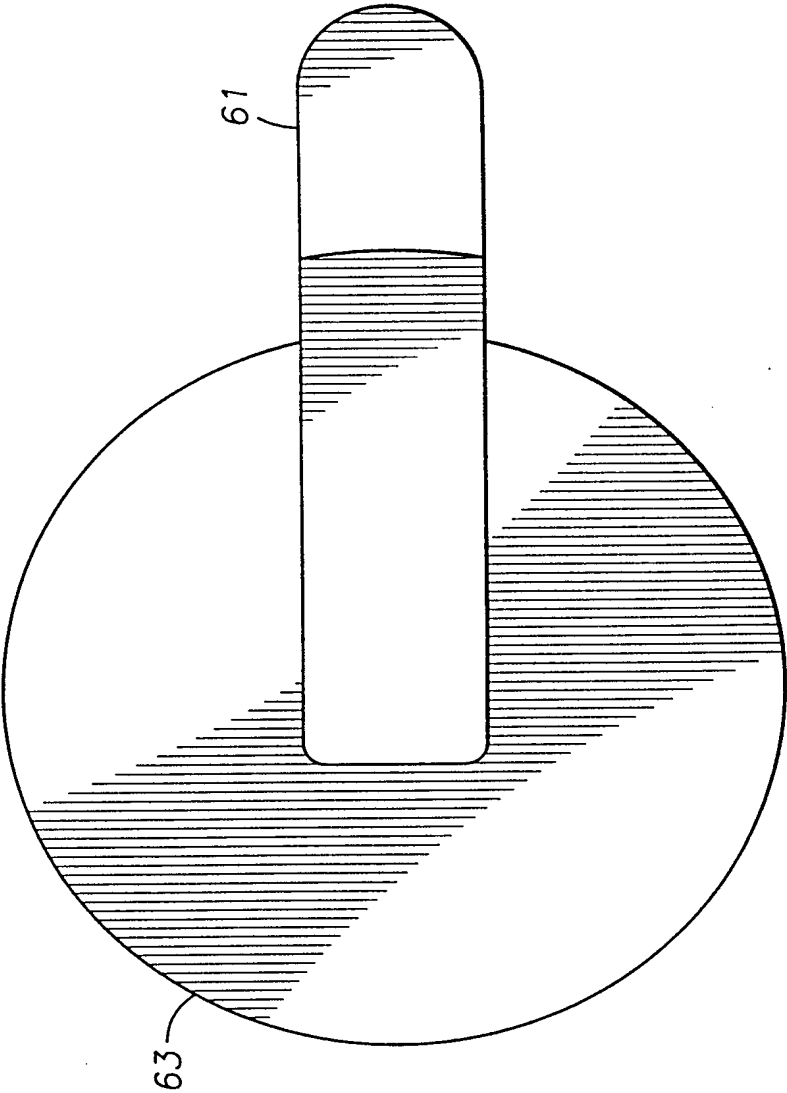


FIG. 9

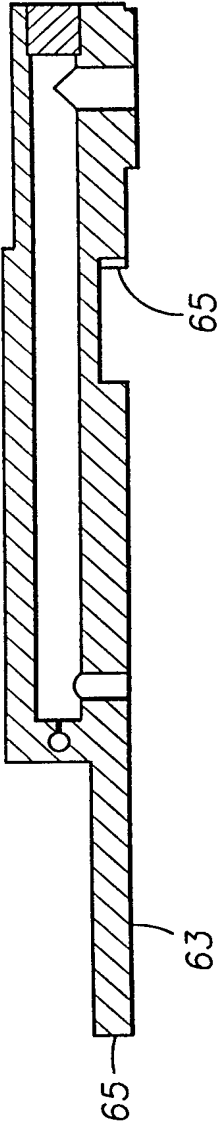


FIG. 10

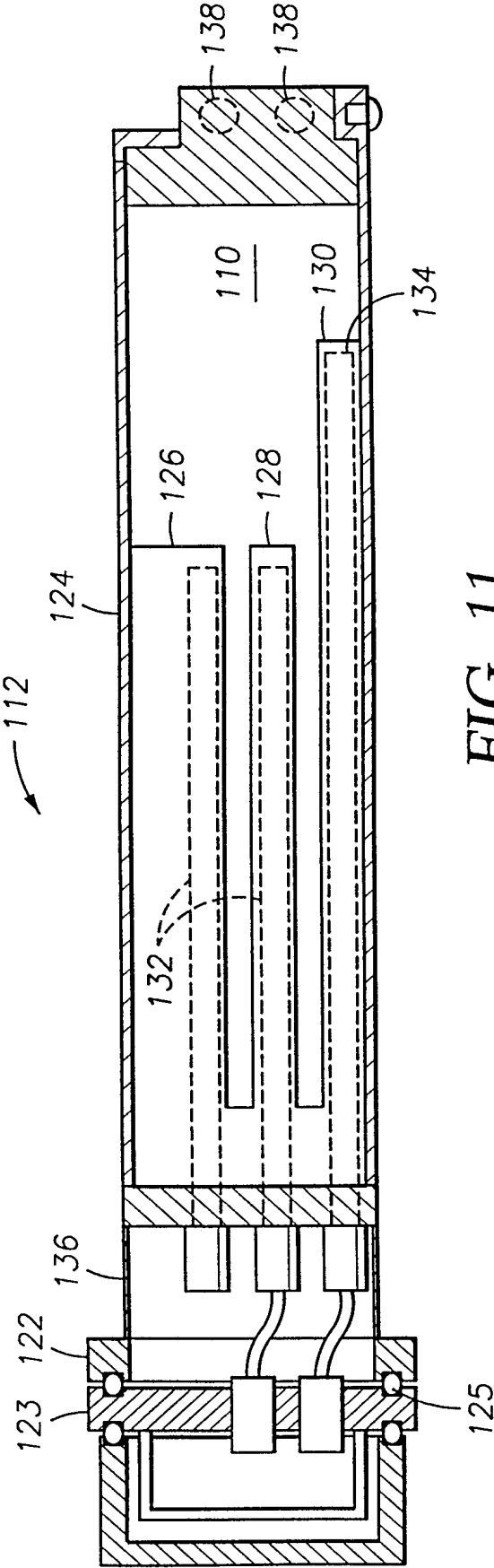


FIG. 11

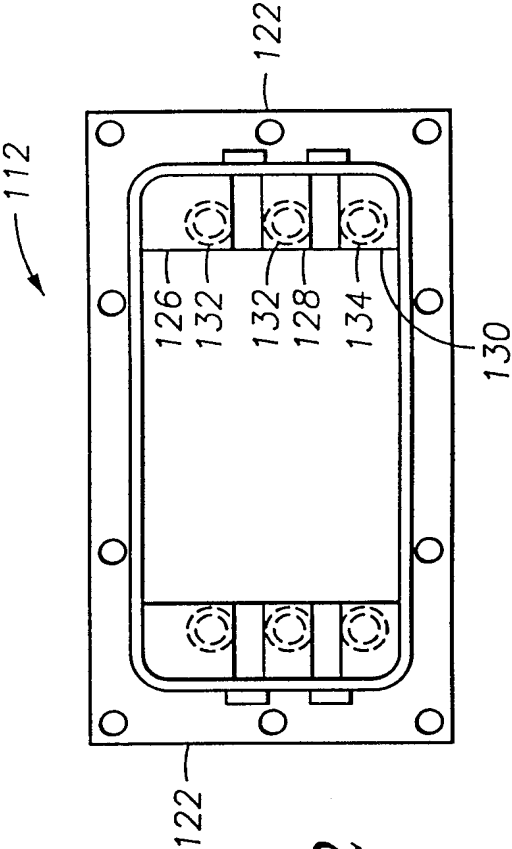


FIG. 12

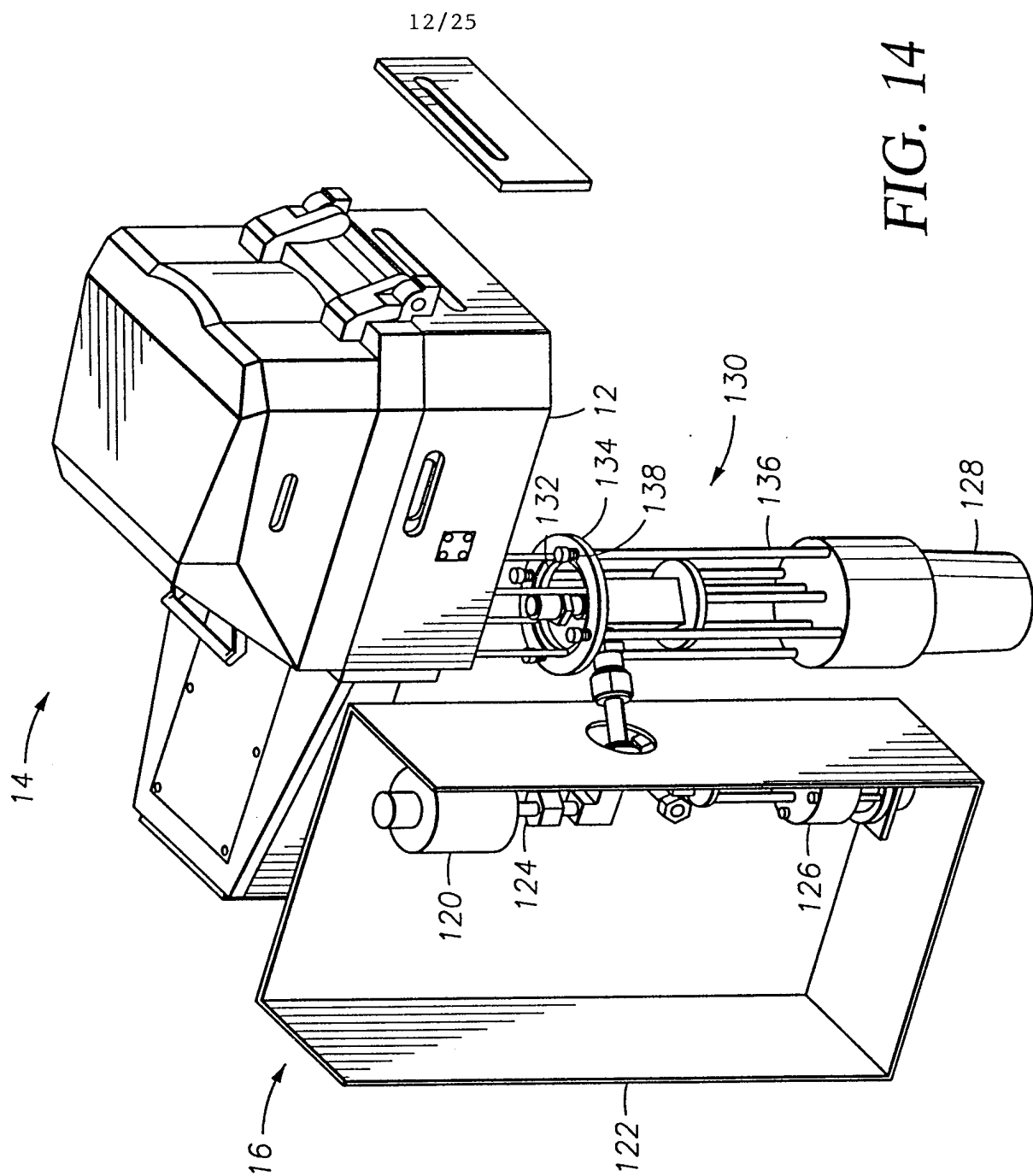
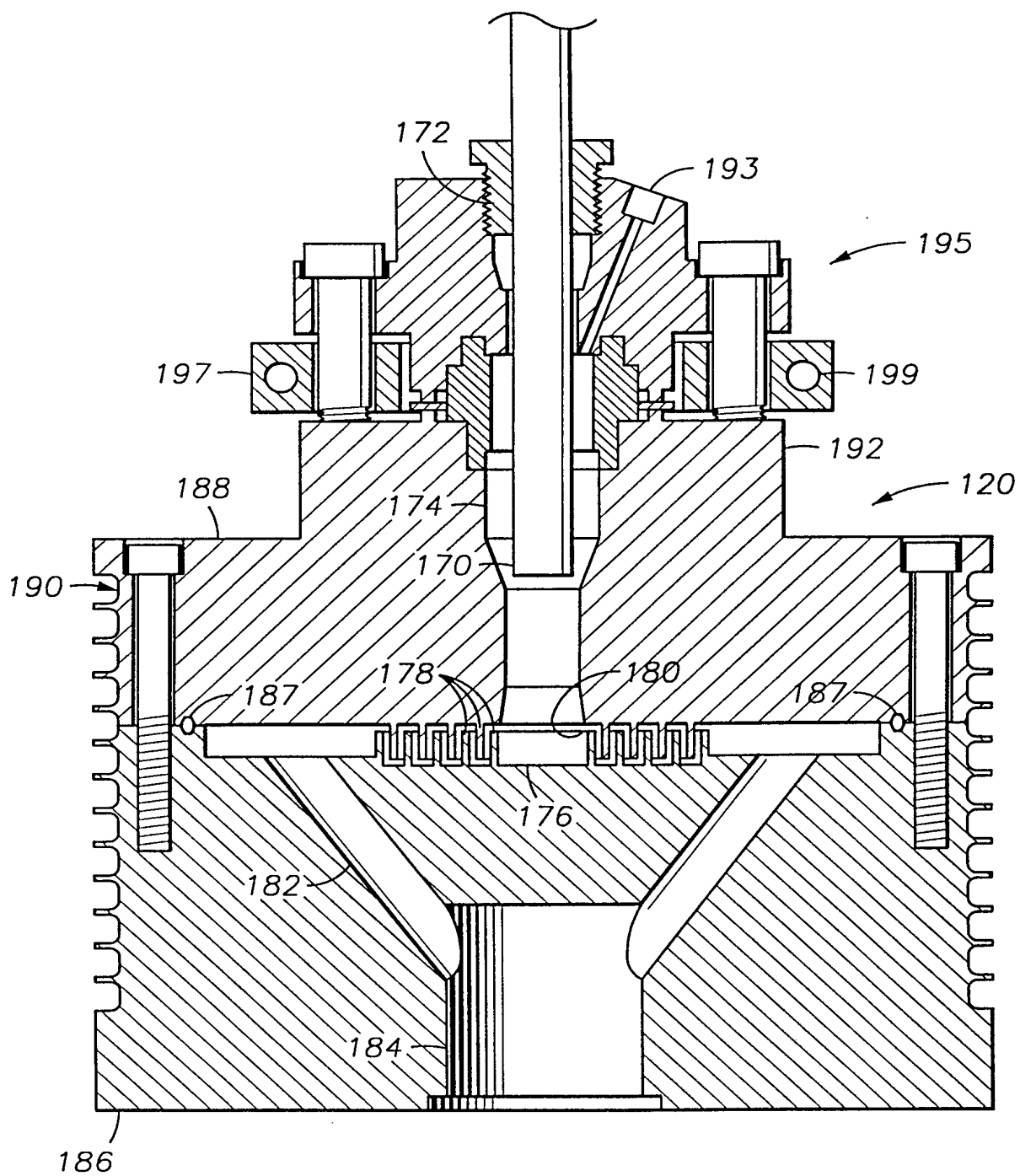


FIG. 14

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*FIG. 15*

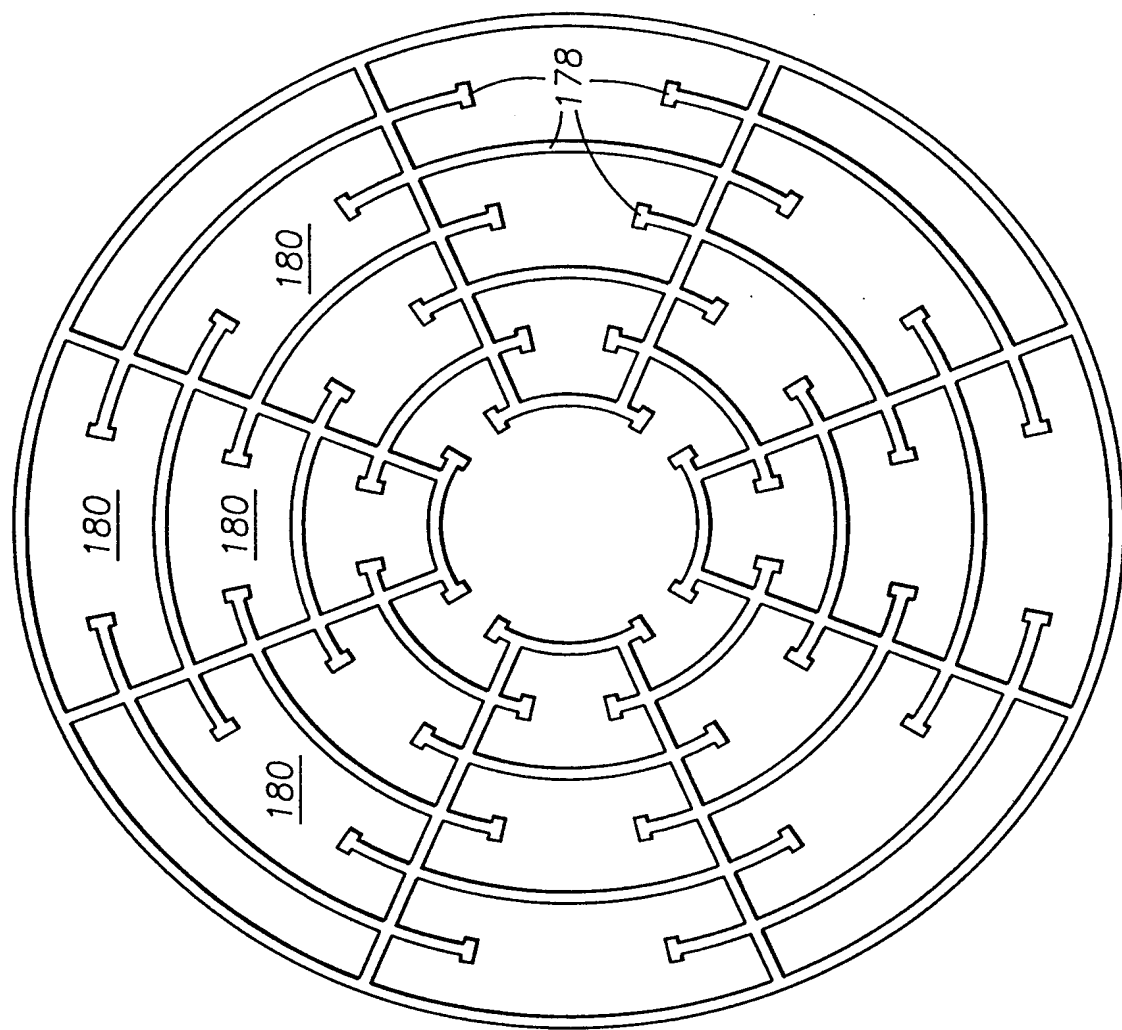


FIG. 16

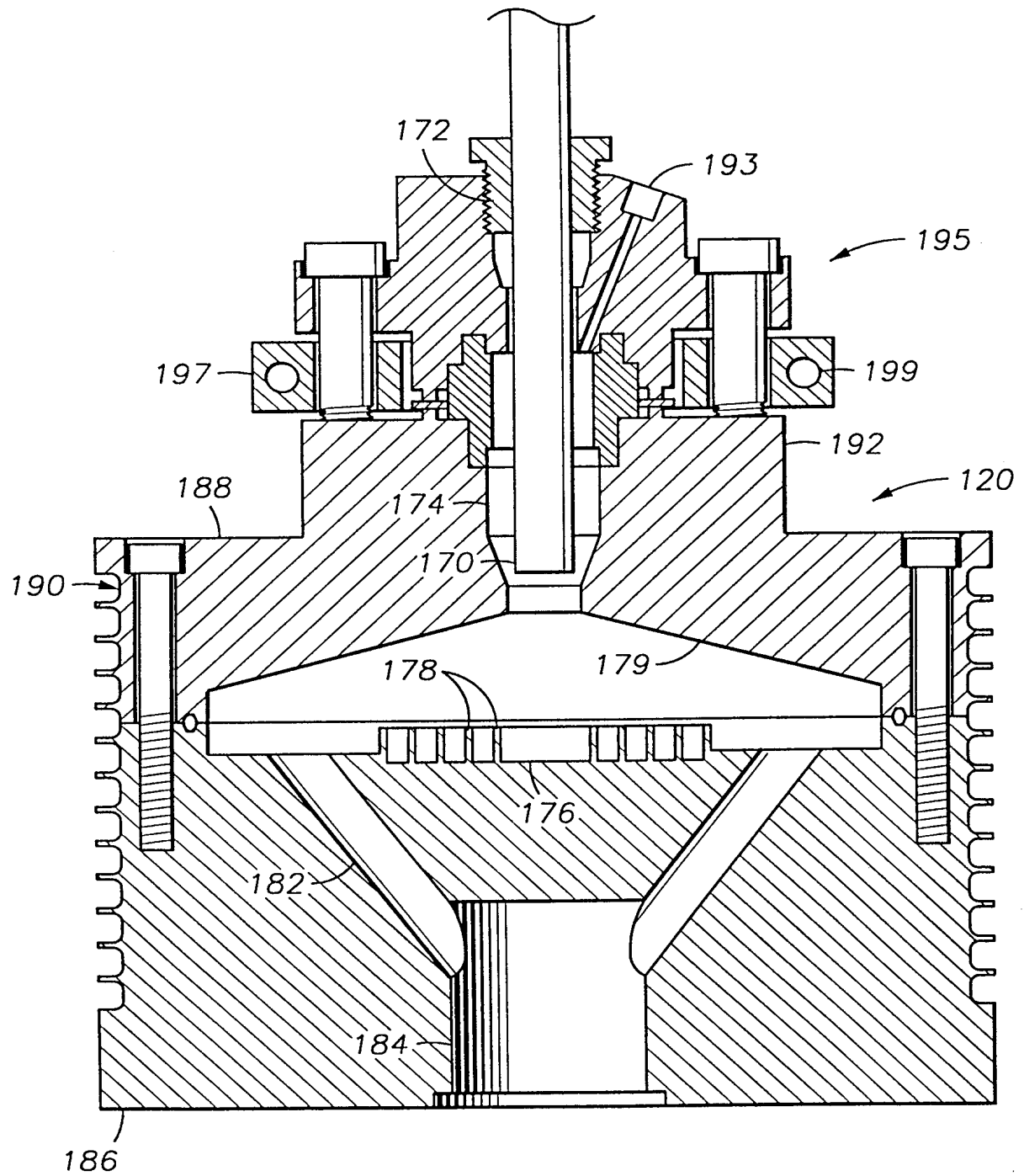
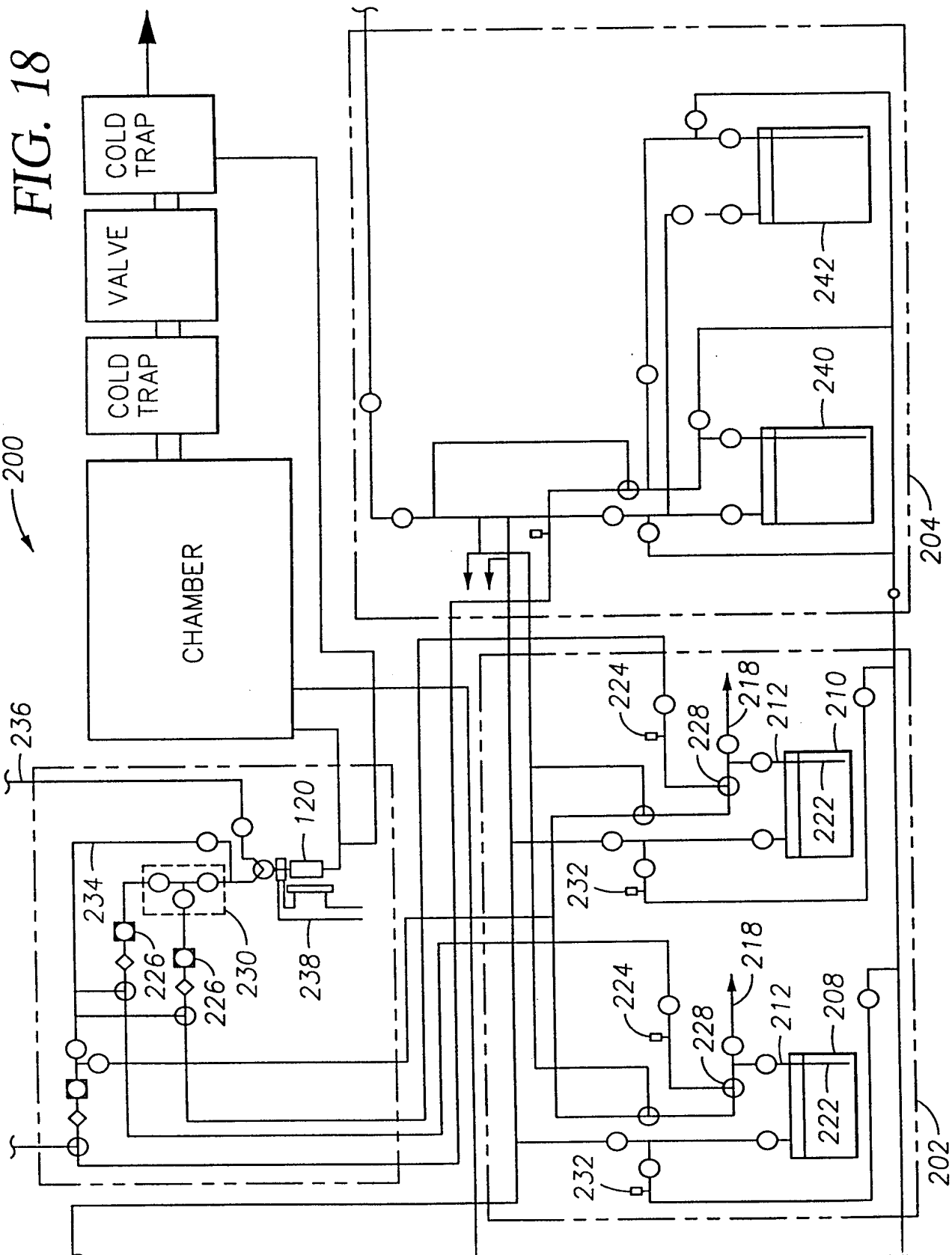


FIG. 17



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FIG. 19

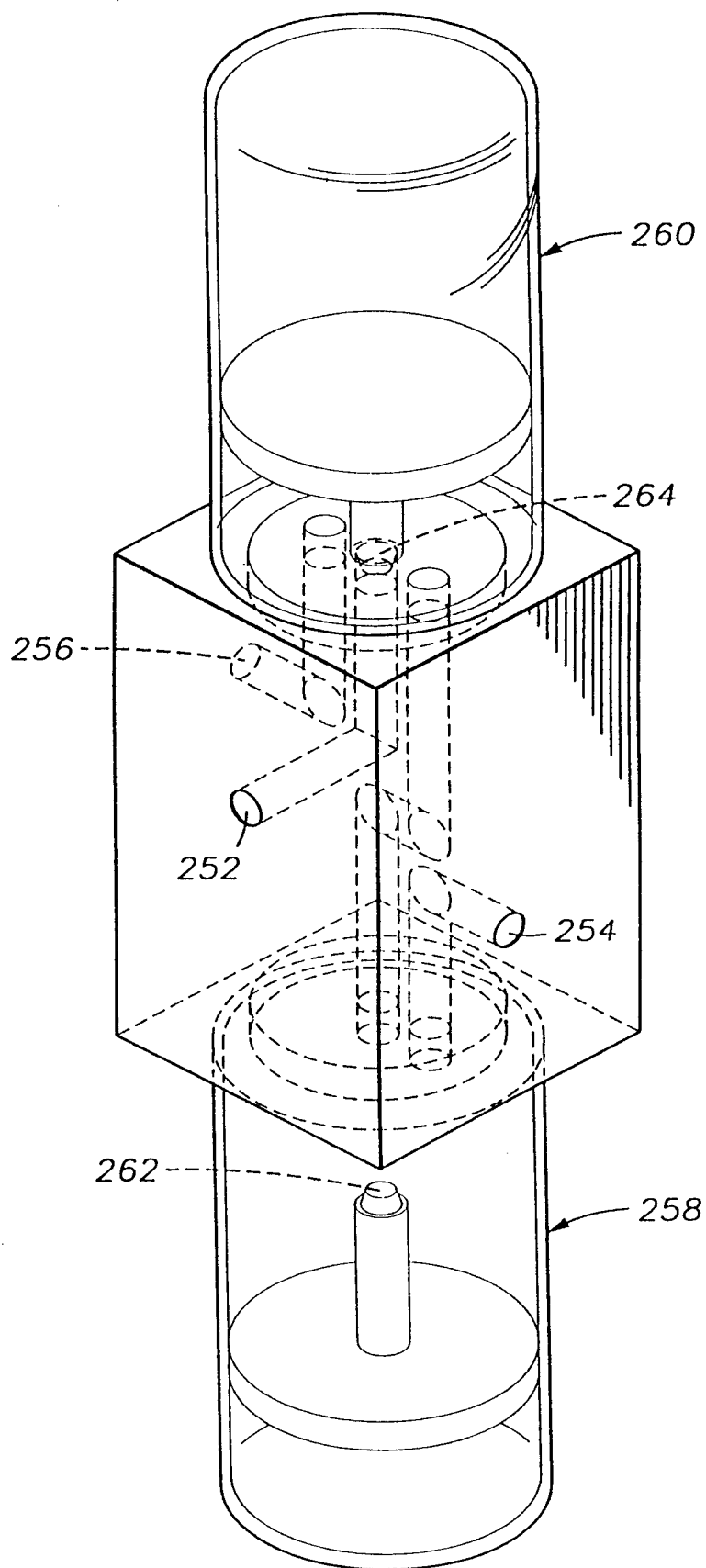
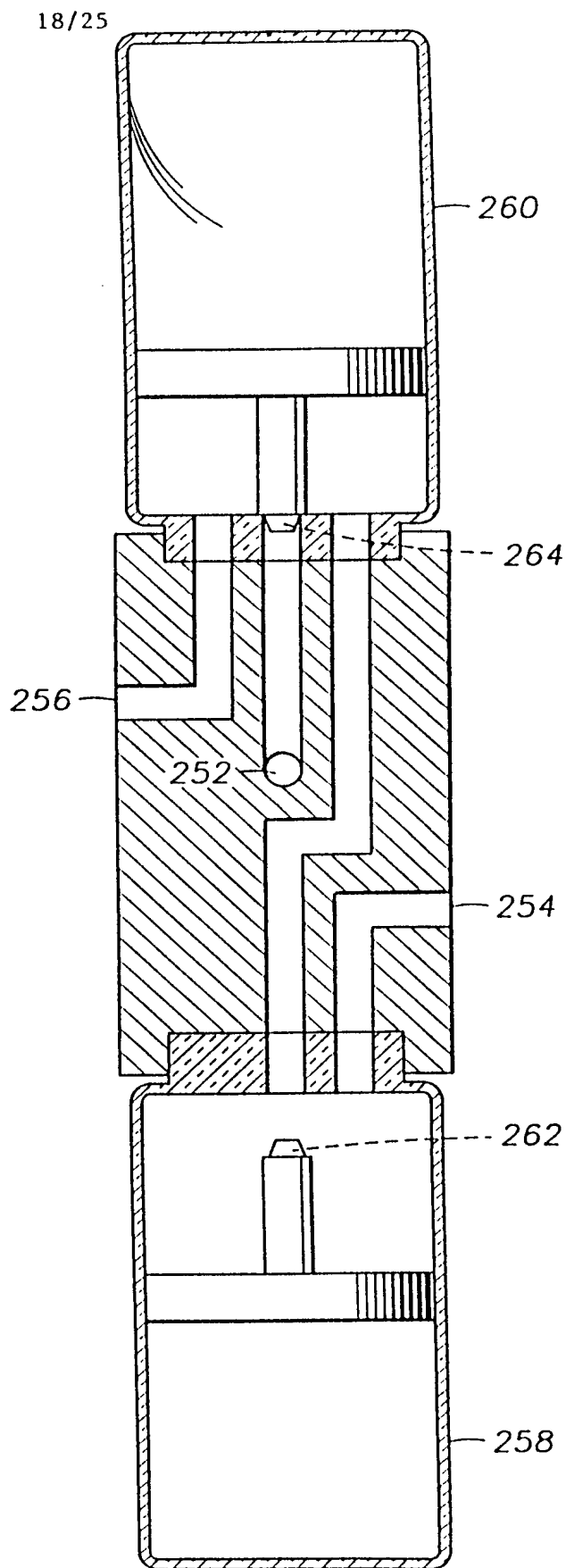


FIG. 20



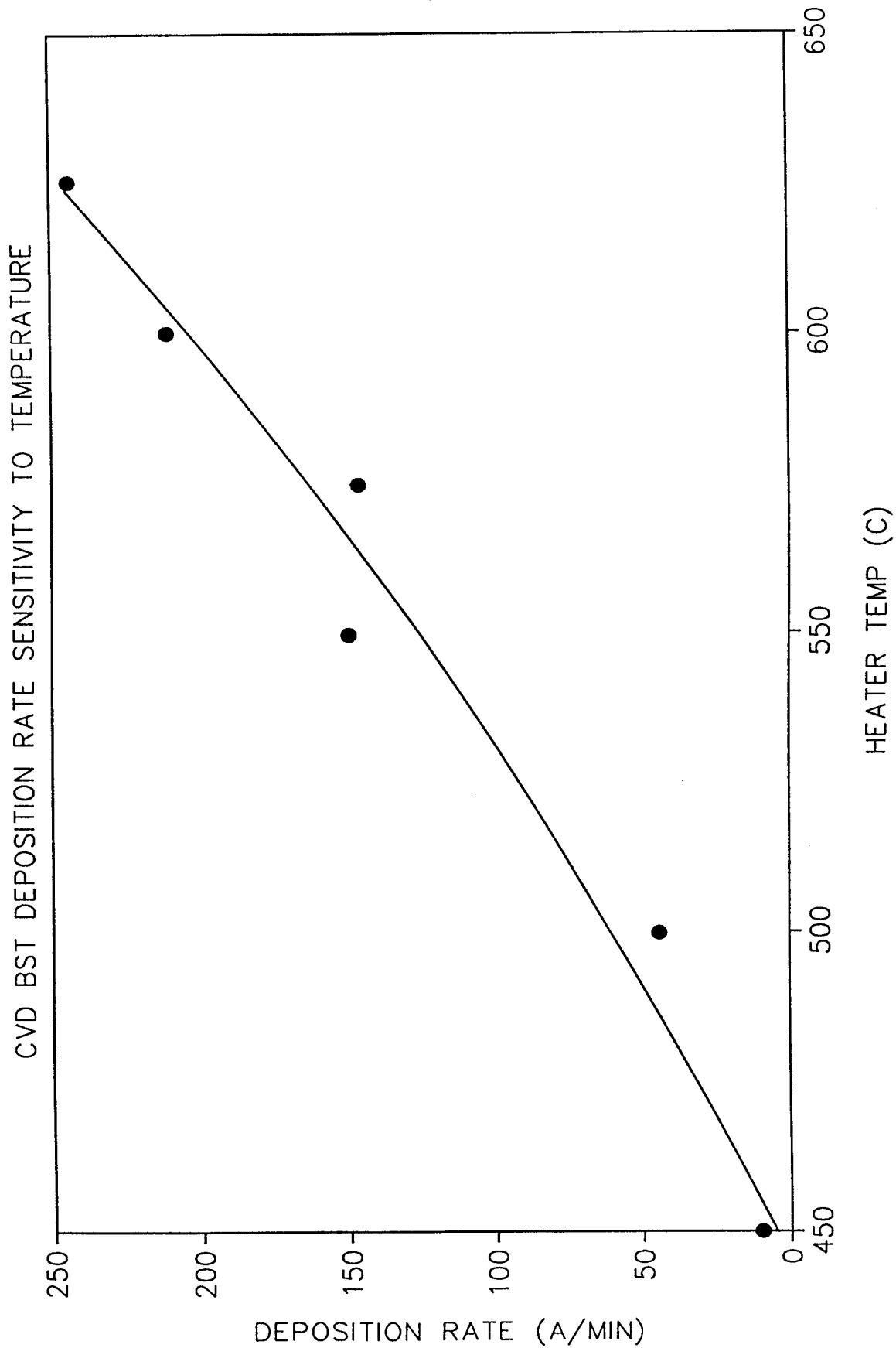


FIG. 21

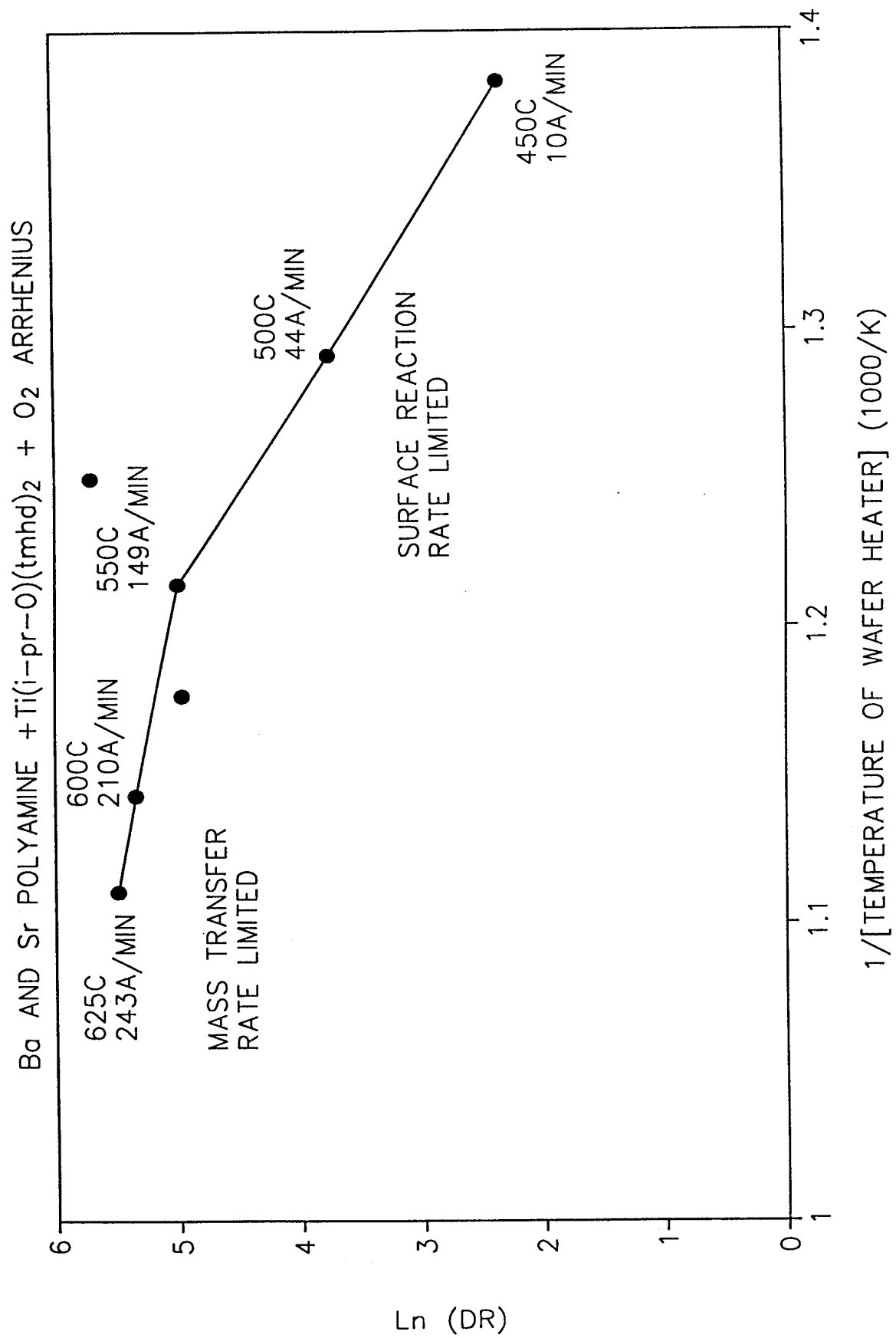


FIG. 22

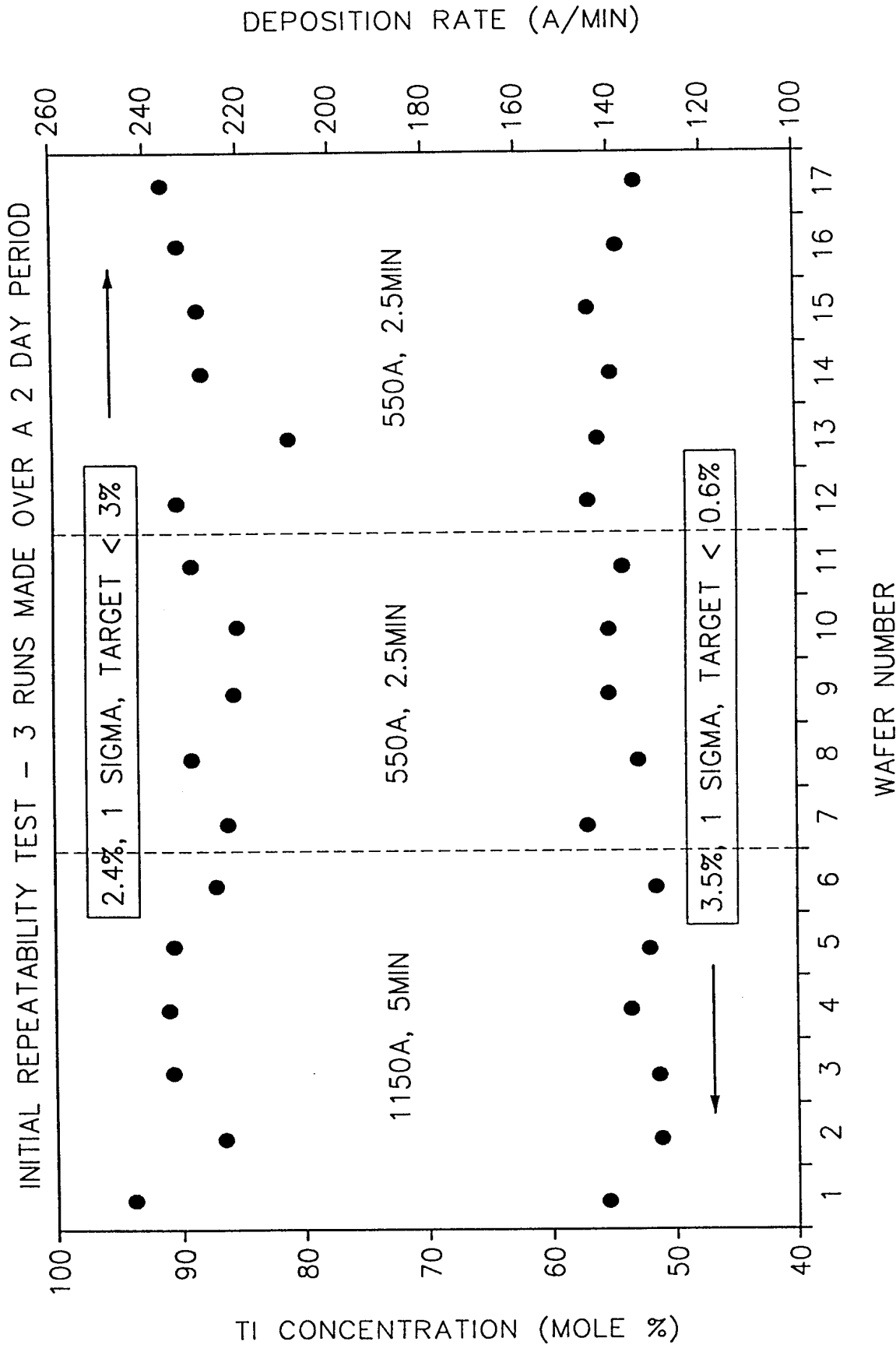


FIG. 23

Ti REPEATABILITY TEST WITH < +/-0.5C WAFER HEATER DURING DEPOSITION

SUBSTRATE	Ti FLOW	Ti MOLE %			Ba MOLE %			Sr MOLE %		
		WAFER		DELTA	WAFER		DELTA	WAFER		DELTA
		1	2		1	2		1	2	
Si PRIME	110	54.6	54.49	0.11	29.48	30.3	-0.82	15.92	15.2	0.72
Si PRIME	100	52.45	52.04	0.41	31.51	33.04	-1.53	16.04	14.93	1.11
Si PRIME	90	52.1	51.7	0.4	31.12	31.77	-0.65	16.77	16.53	0.24
Pt / OX/ 1 Si RECI	110	65.34	61.48	3.86	22.54	25.73	-3.19	12.11	12.78	-0.67
Pt / OX/ 2 Si RECI	100	60.03	60.5	-0.47	26.75	26.16	0.59	13.22	13.34	-0.12
Pt / OX/ 1 Si RECI	90	61.8	60.9	0.9	24.44	26.2	-1.76	13.75	12.87	0.88

FIG. 24

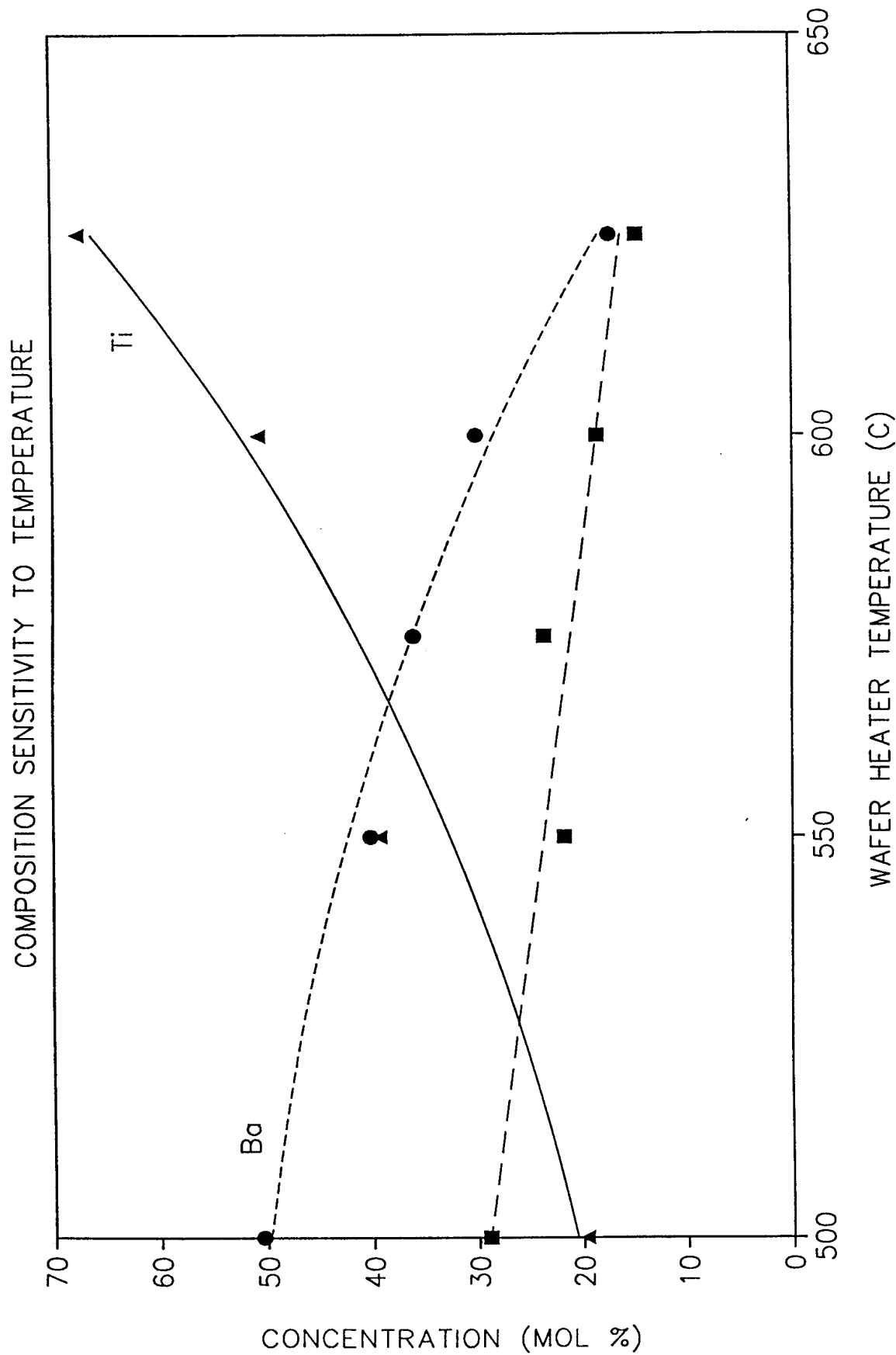


FIG. 25

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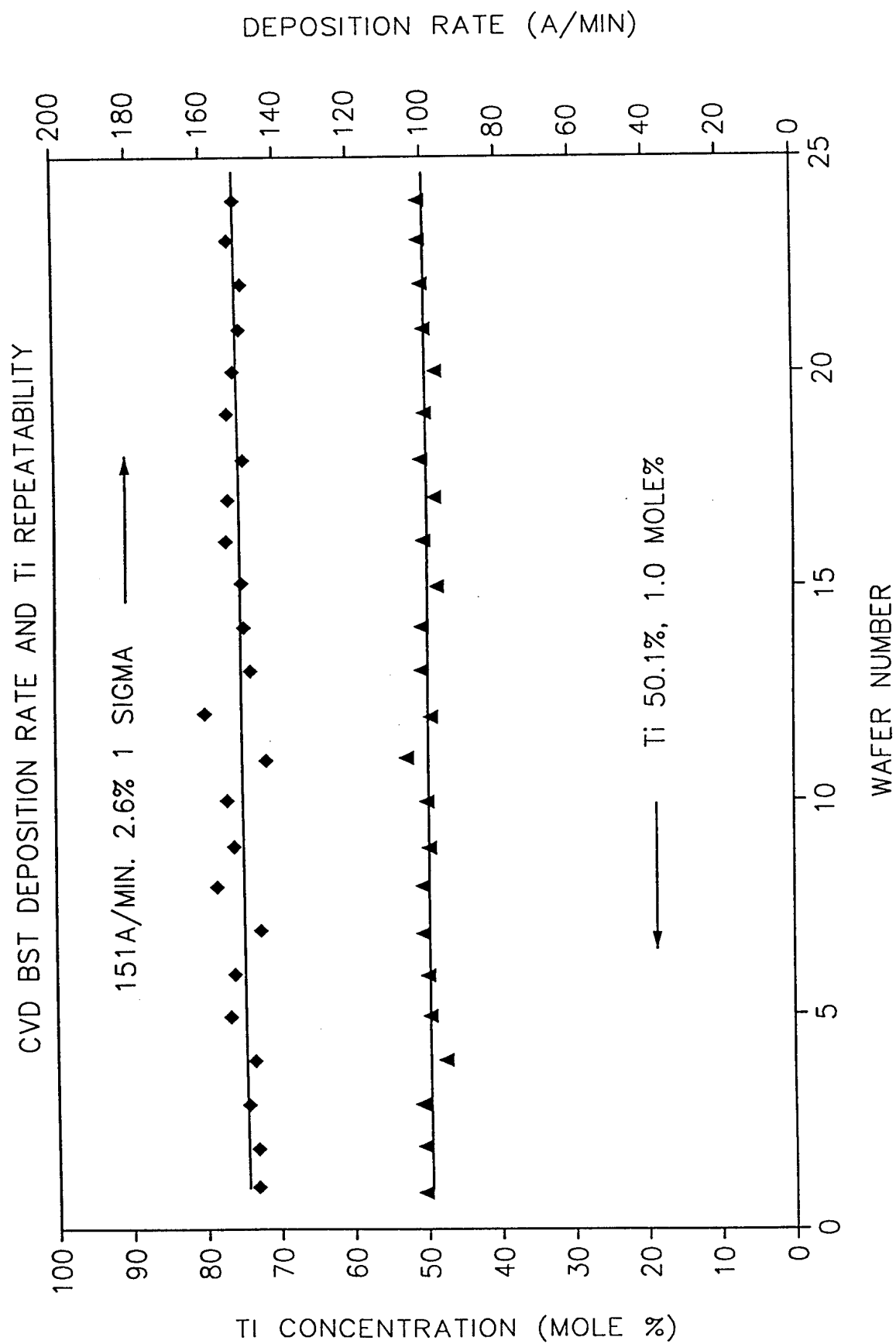


FIG. 26

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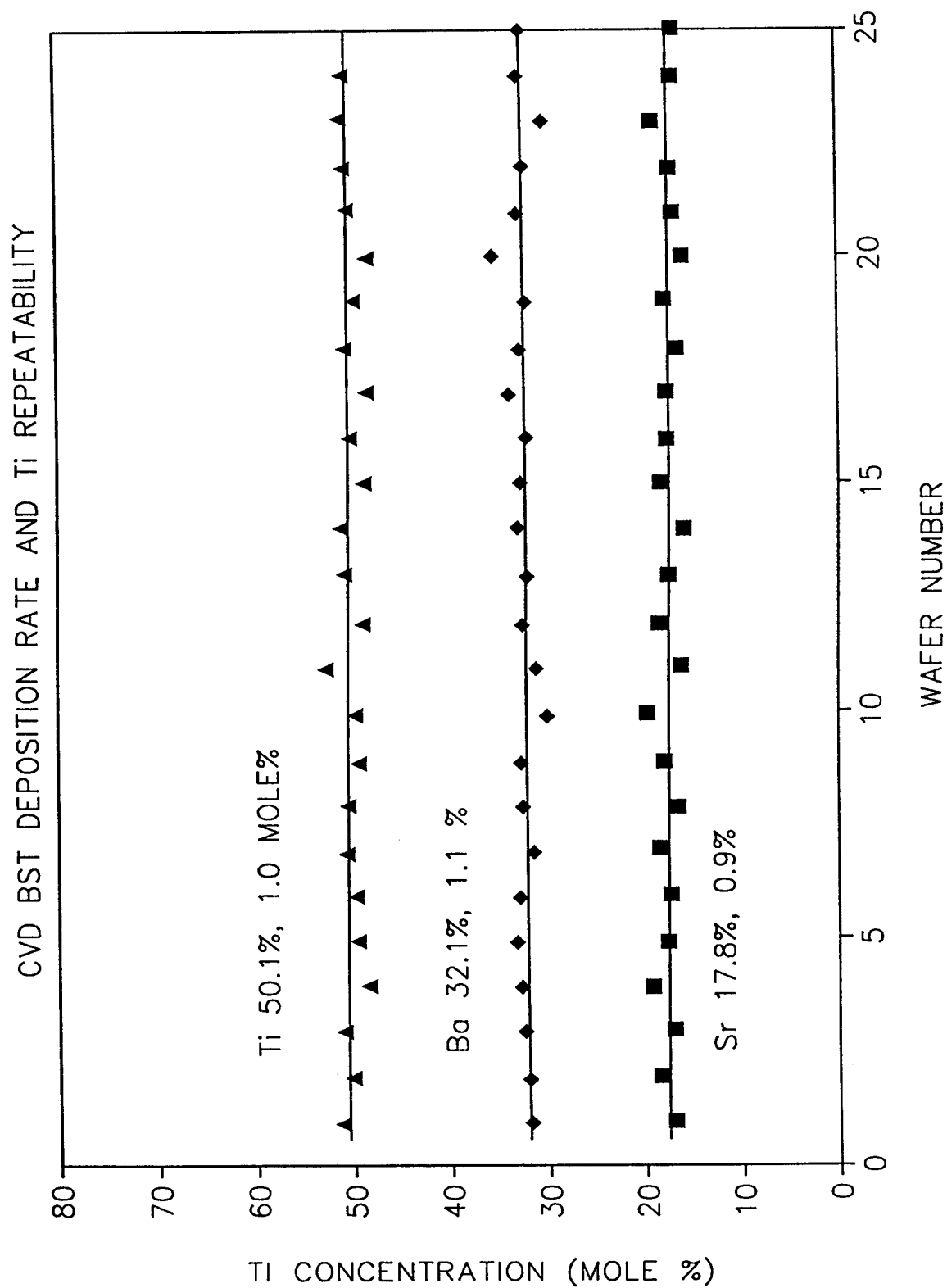


FIG. 27